

RF SoCの現状と今後の展開

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- **Introduction**
- **RF-CMOS SoC for FM/AM tuner**
- **DRP: Digital RF Processing SoC**
- **mm-wave SoC**
- **Conclusion**

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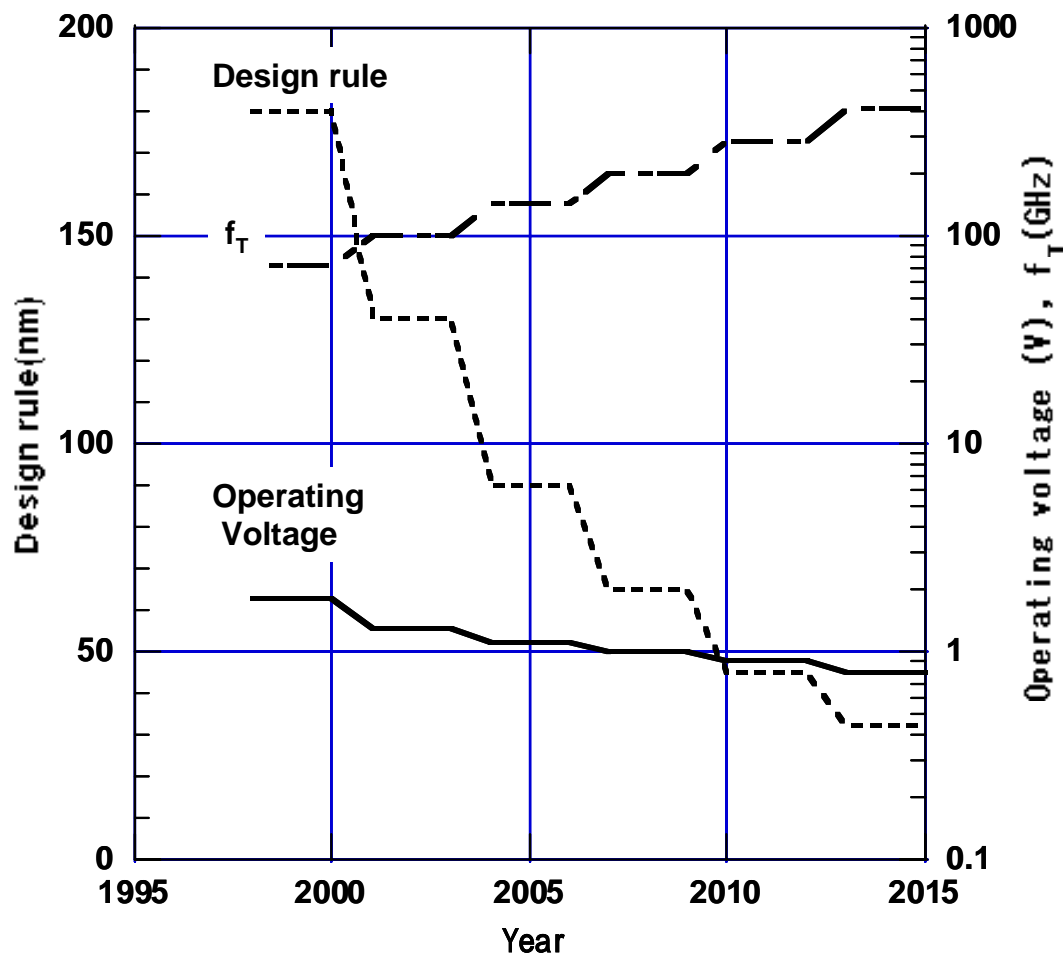
Why CMOS?

- **Low cost**
 - Must be biggest motivation
 - CMOS is 30-40% lower than Bi-CMOS
- **High level system integration**
 - CMOS is one or two generation advanced
 - **CMOS can realize full system integration**
- **Stable supplyment and multi-foundries**
 - Fabs for SiGe-BiCMOS are very limited.
→ Slow price decrease and limited product capability
- **Easy to use**
 - Universities and start-up companies can use CMOS with low usage fee, but SiGe is difficult to use such programs.

f_T and operating voltage of CMOS

f_T is higher than 200GHz at 90nm NMOS and enables mm-wave application.

Operating voltage will be around 1V.



$$f_T \approx \frac{v_s}{2\pi L}$$

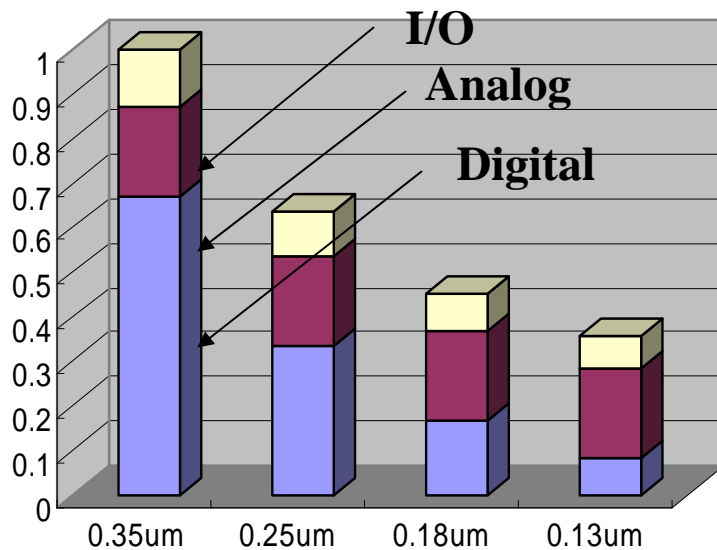
v_s : Saturation carrier velocity
 L : Channel length

Cost up issue by analog parts

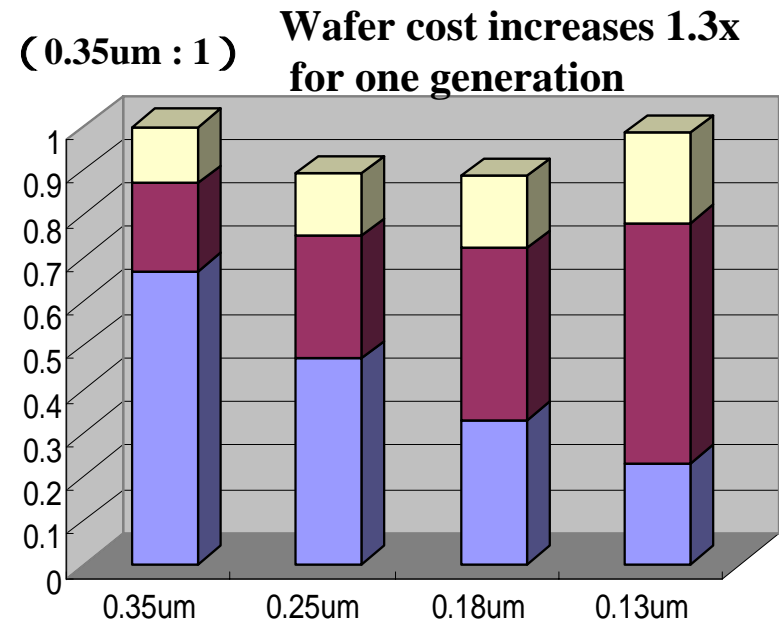
Cost of mixed A/D LSI will increase when using deep sub-micron device, due to the increase of cost of non-scalable analog parts.

Large analog may be unacceptable.

Some analog circuits should be replaced by digital circuits



Chip area



Chip cost

Akira Matsuzawa, "RF-SoC- Expectations and Required Conditions,"
IEEE Tran. On Microwave Theory and Techniques, Vol. 50, No. 1, pp. 245-253, Jan. 2002

Analog centric RF CMOS will be replaced by digital centric RF CMOS.

Wireless LAN, 802.11 a/b/g
0.25 μ m, 2.5V, 23mm², 5GHz

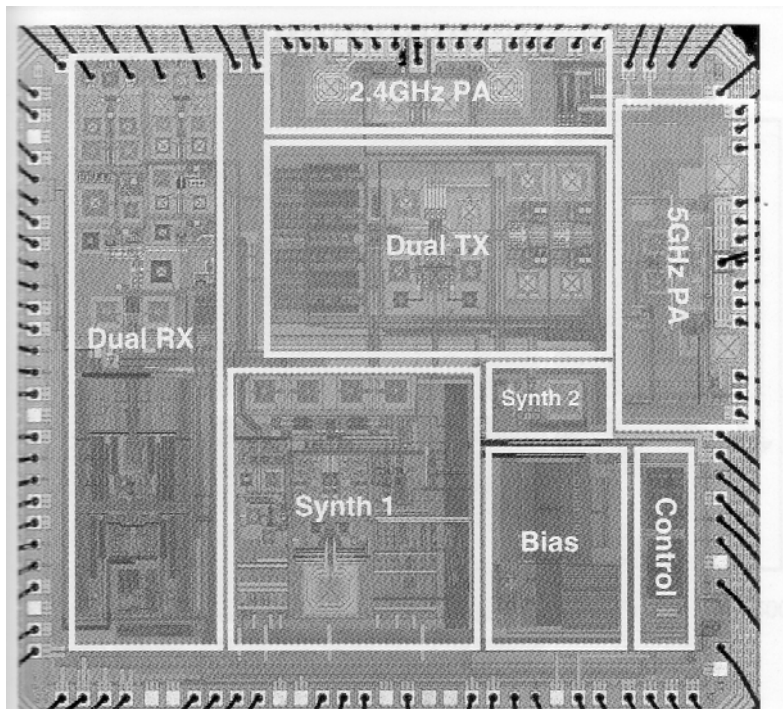


Figure 5.4.7: Die micrograph.

M. Zargari (Atheros), et al., ISSCC 2004, pp.96

Discrete-time Bluetooth
0.13 μ m, 1.5V, 2.4GHz

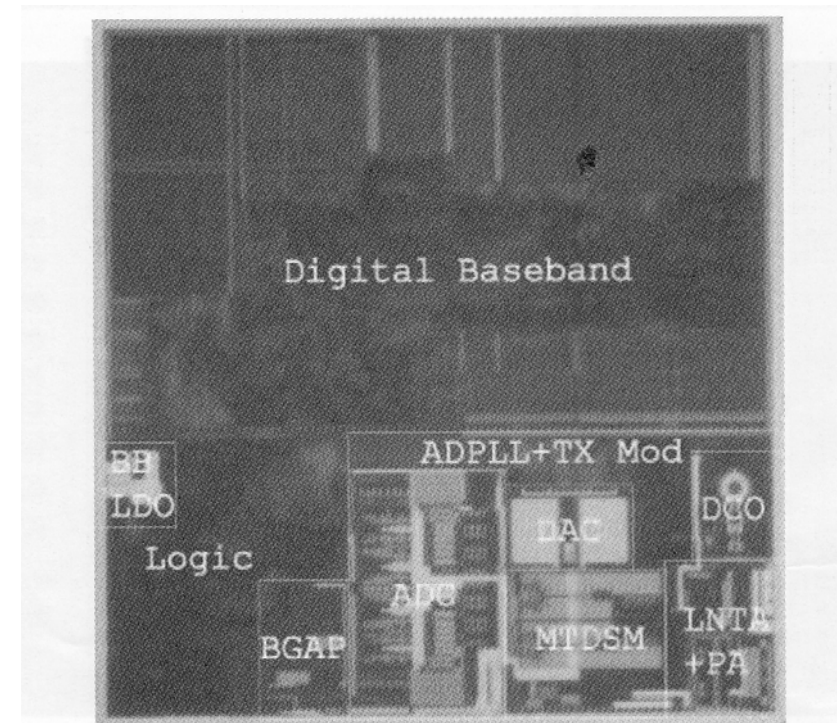
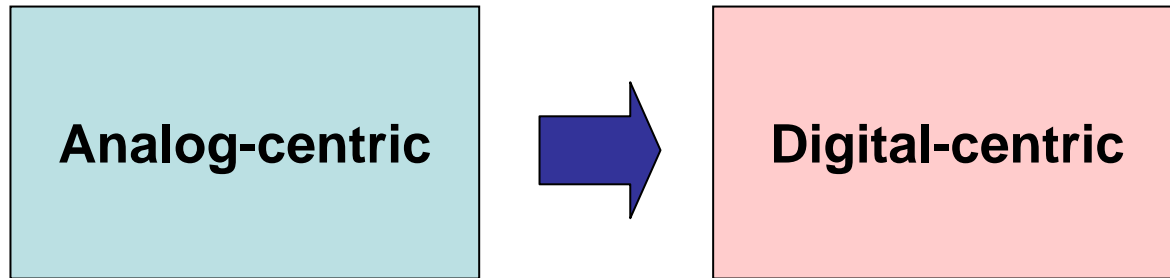


Figure 15.1.7: Die micrograph of the single-chip Bluetooth transceiver.

K. Muhammad (TI), et al., ISSCC2004, pp.268

Technology trend in RF-CMOS LSI

Analog-centric RF CMOS will be replaced by digital-centric RF CMOS. High performance, low cost, stable and robust circuits, no or less external components, no adjustment points, and high testability are the keys. DSP and ADC will play important role.



Signal processing

Analog circuits
Analog processing
+External component

DSP+ADC
+ Small and robust analog ckts.

Adjustment

External

Digital on chip, no external

External components Large #

No or less

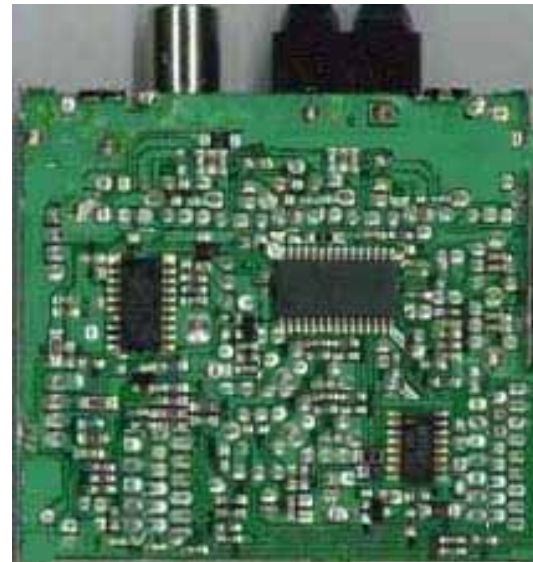
RF-CMOS SoC for FM/AM tuner

Courtesy Niigata-Seimitsu Co., Ltd.

Current AM/ FM tuner system

Current AM/FM tuner uses 3 ICs and large # of external components.
Furthermore 12 adjustment points are needed.

Large # of products, but not expensive product.
More efforts for the cost reduction are still needed.

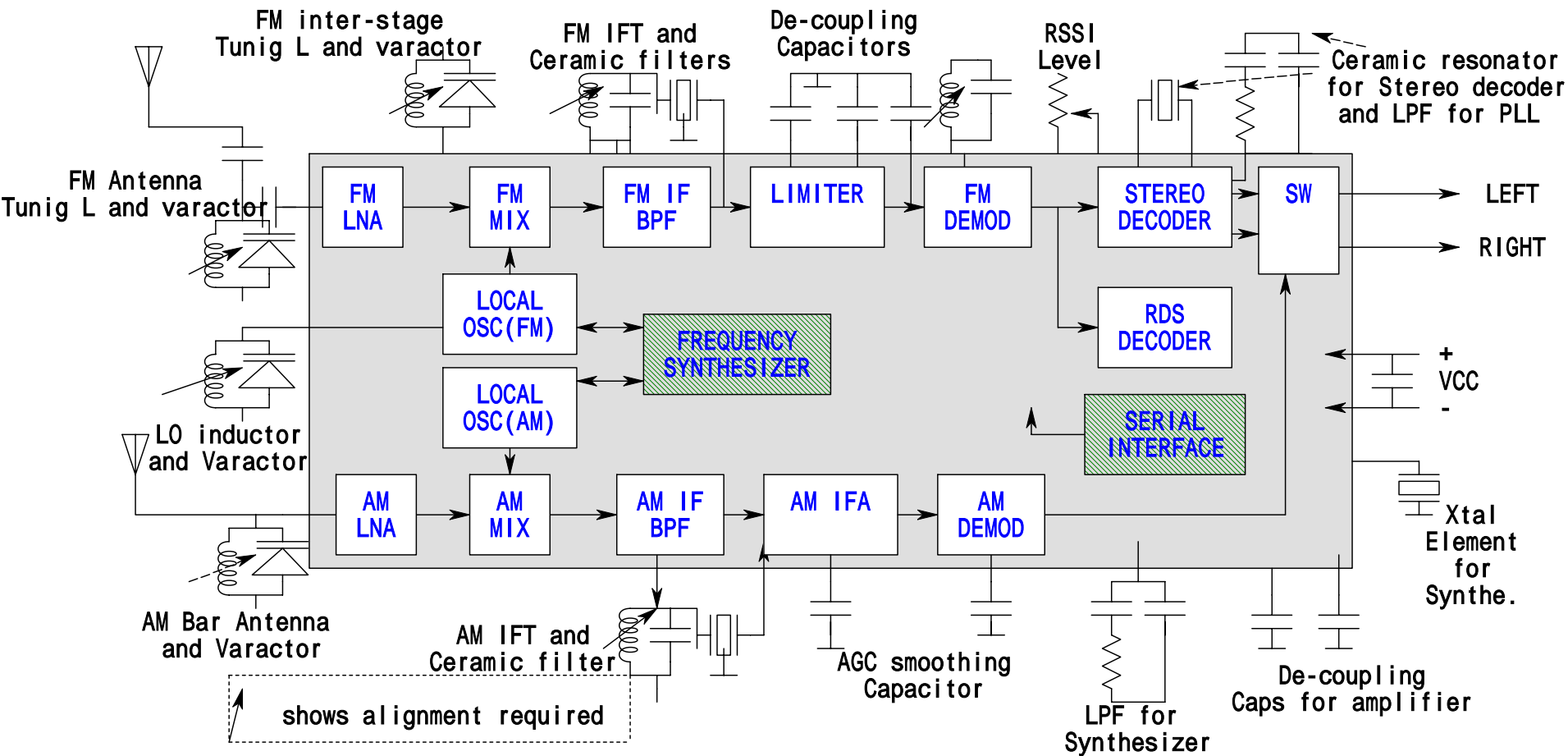


Bipolar IC = 1 (RF)
CMOS IC = 2 (PLL, RDS)
External Components=187

AM/FM Tuner for home use
12 adjustment points

Block diagram of current FM/AM tuner

Large # of external components. They should be integrated on a chip.



External parts used in existing IC

Large # of external components are needed to analog signal processing.

External Parts	Blocks to be used
System	FM: Single conversion super heterodyne. IF=10.7MHz AM: Single or Double conversion super heterodyne IF=450KHz or 10.7MHz + 450KHz
Resistor	AGC, bias, LPF for PLL
Semi-fixed and Variable resistor	RSSI level alignment, volume control
Ceramic capacitor Small value capacitor	RF bypass, coupling, de-coupling
Electrolytic capacitor	AGC smoother, power-ground decoupling
Inductor	RF tuning, local oscillator, IF transformer, FM detector
Variable capacitance	RF tuning, Local oscillator
Analog filter	Noise canceller, LPF
Ceramic filter	FM and AM IF BPF for channel filter
Xtal Osc. element	System clock, Reference for PLL synthesizer
Total number of external parts	Home tuner and radio cassette tuner : around 165pcs Car tuner : 80 to 130pcs

Application of CMOS technology to AM/FM tuner looks very difficult, due to lower frequency and high dynamic range.

Lower frequency AM: 522 KHz to 1710 KHz
SW: 2.3MHz to 26MHz
FM: 87.5 to 108 MHz

Larger Inductance and capacitance → **External components**

Serious 1/f noise → **Bipolar**

High dynamic range

AM: 14 dBuV to 126 dBuV
FM: 0 dBuV to 126 dBuV

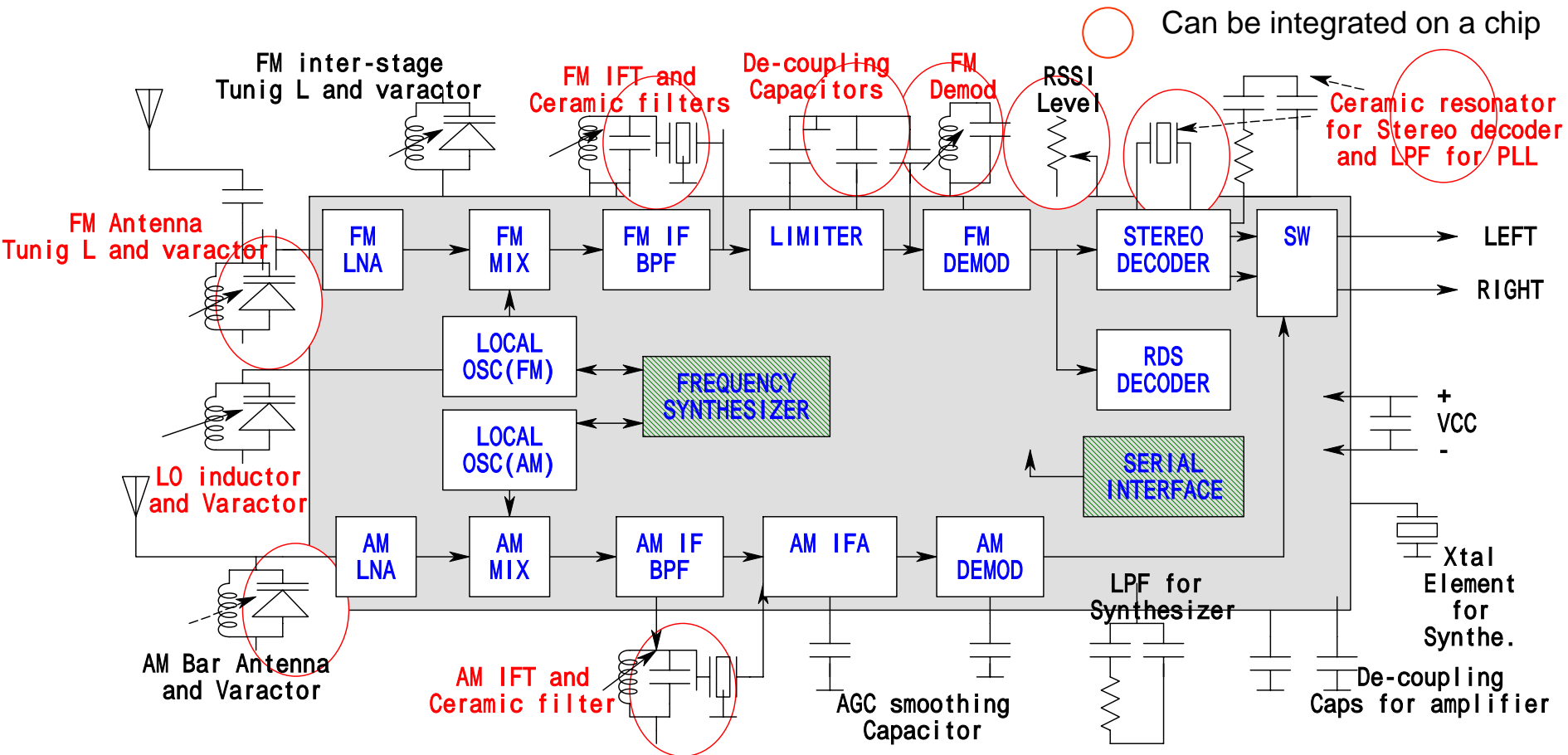
Sharp and fine filter → **External filters (Ceramic)**

External varactors

High linearity ckt. → **Bipolar**

1st trial by CMOS technology

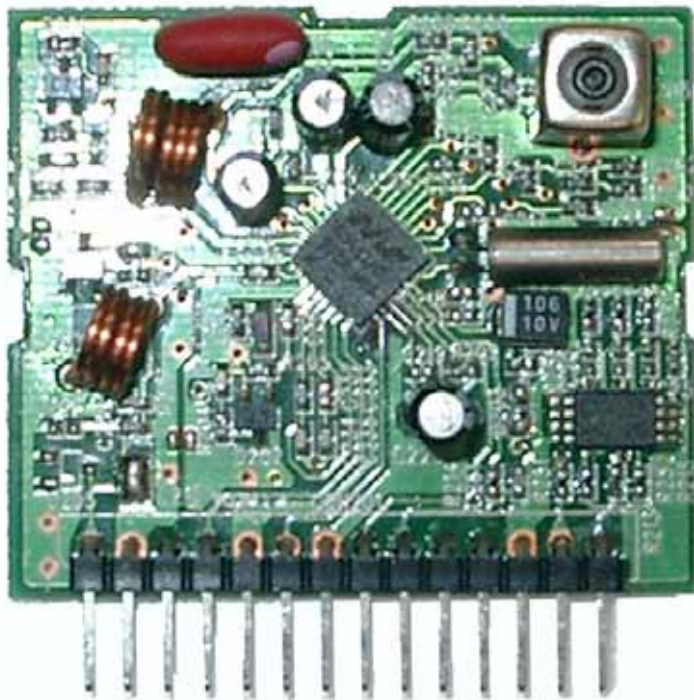
1st trial to realize AM/FM tuner by CMOS technology, many external components should be reduced.



Characteristics is affected by process variation easily.

Element mismatch causes DC offset, noise, distortion, and low filter performance.

The reduction of # of external components is not attractive for users.



External components 187 → 69

1st trial was analog-centric CMOS tuner technology.

Circuits have been replaced by CMOS, however still use analog technology. Thus it had many issues and many external components were still needed.

Parts	Methods for on-chip	Problems
AM/FM IF BPF	1. Low IF(a few hundred KHz) 2.Gm-C BPF with auto alignment, SCF	1.poor selectivity(-45dB), 2. SCF Switch noise 3. Center frequency shift by DC offset 4. Poor image rejection ratio (25 to 35dB)
FM Demodulator	Pulse count FM detector	Poor THD (0.5%)
Stereo Decoder	Multi-vibrator VCO, SCF filter	Large variation of free-run frequency Still need external LPF for PLL
RSSI Level adj.	Signal detector with DC compensation	Can't cover all process corner
Varactor	MOS varactor	Too much sharp C-V curve, distorted signal
AGC smoother	Time division charge and discharge	Needs large capacitor for low audio frequency
Capacitors	Stages Direct connection, use small value coupling capacitor	High impedance required, Difficult for low frequency

Lower frequency AM: 522 KHz to 1710 KHz
SW: 2.3MHz to 26MHz
FM: 87.5 to 108 MHz

Larger Inductance and capacitance → **Digital filter, Mixer, PLL
GHz OSC with divider**

Serious 1/f noise → **PMOS**

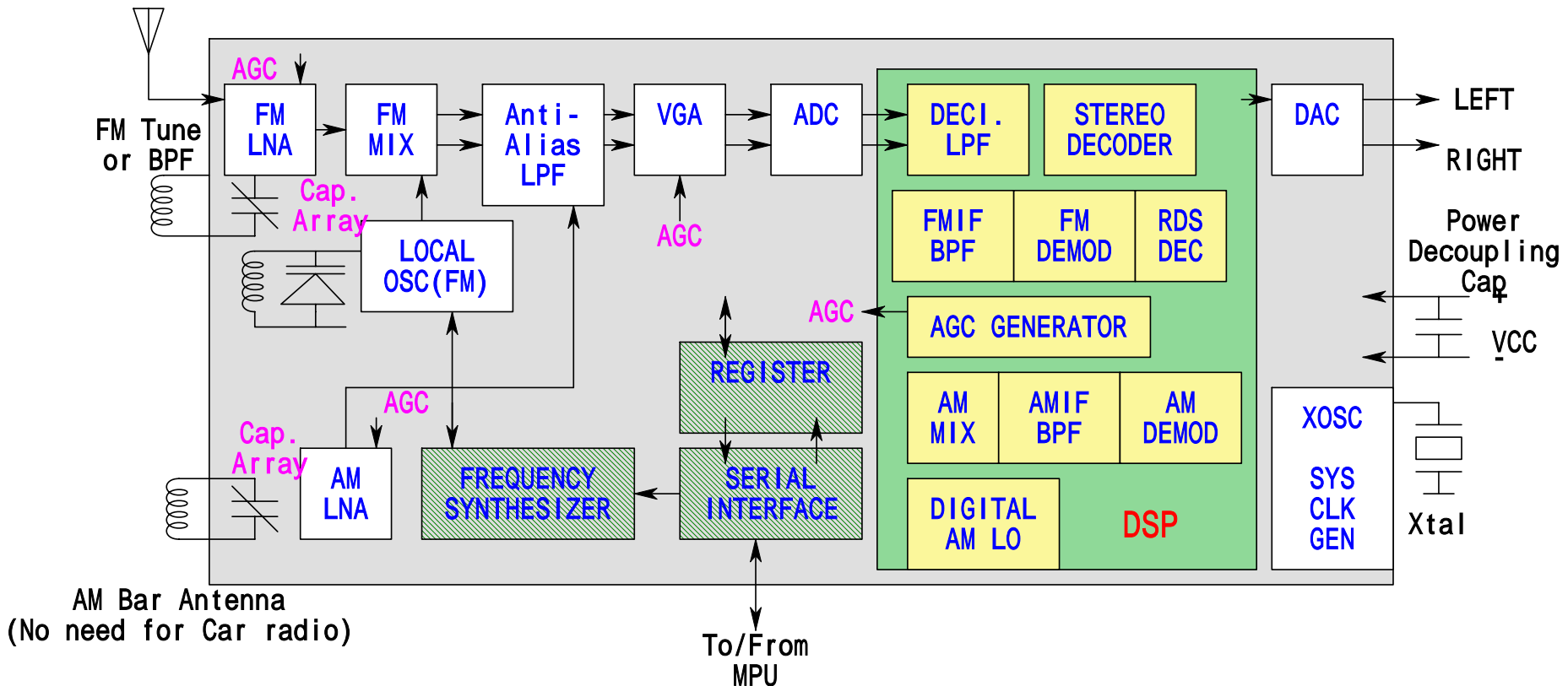
Larger signal dynamic range AM: 14 dBuV to 126 dBuV
FM: 0 dBuV to 126 dBuV

Sharp and fine filter → **Digital Signal processing
With high resolution ADC
IF Freq. changed from
10.7 MHz to several 100 KHz**

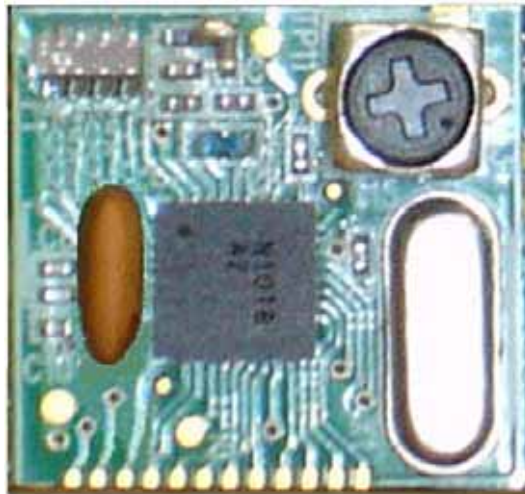
High linearity ckt. → **High resolution ADC
Switch mixer
Watching desired and undesired signals**

Advanced CMOS tuner

Digital-centric CMOS tuner has been developed.



**One-chip CMOS tuner has been successfully developed.
It can attain high tuner performance and
can reduce the # of external components.
Furthermore it can realize no adjustment points.**



Full CMOS one-chip solution

of external components are 11

No adjustment points

Sensitivity: FM: 9dBuV, AM: 16dBuV

Selectivity: FM/AM >65dB

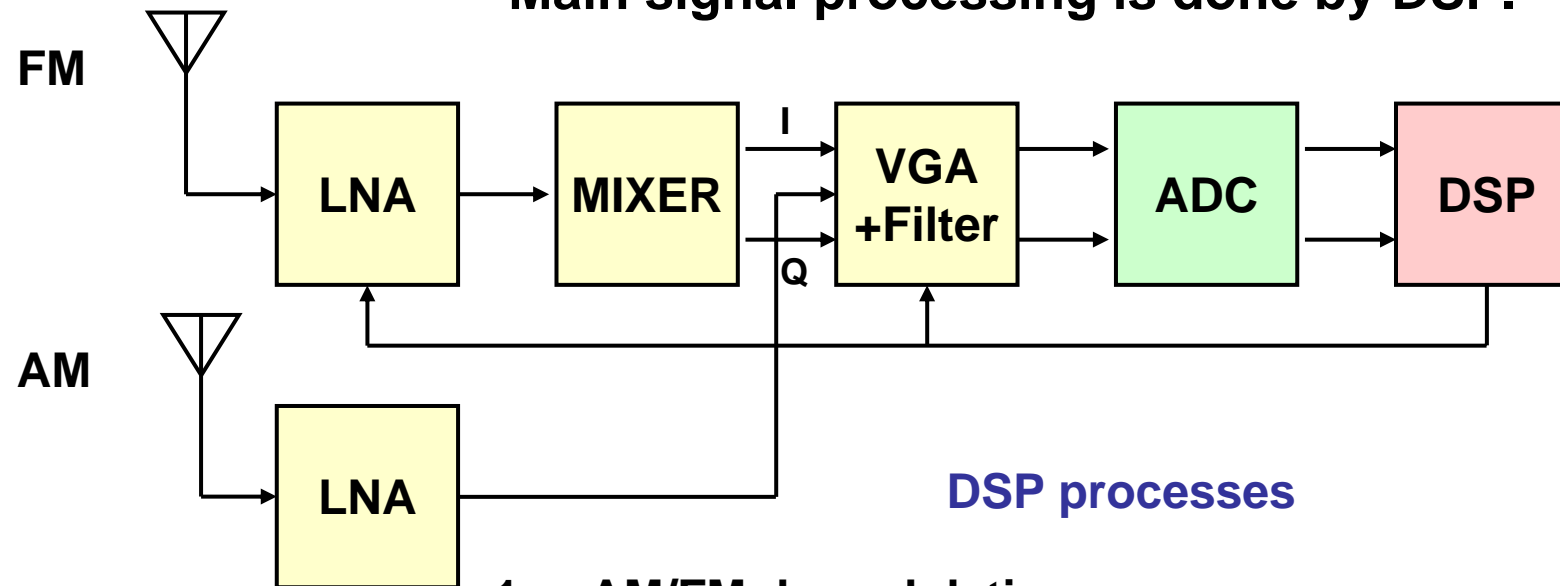
SNR: FM: 63dB, AM: 53dB

Stereo sep: 55dB

Image ratio: FM: 65dB, AM: Infinity

Distortion: FM: 0.09%, AM=0.25%

Main signal processing is done by DSP.



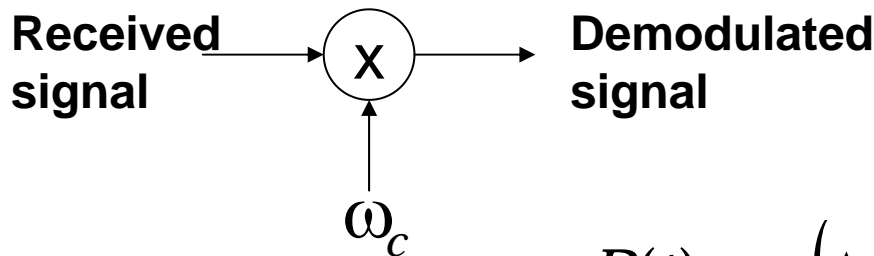
1. AM/FM demodulations
2. Stereo decoder
3. AM mixer
4. Channel select filter
5. Support for image reject
6. Watch the signal level and control gain of each stage
7. Parameter control and adjustment with MCU

Demodulation of AM/FM signal

AM/ FM signals can be demodulated by simple arithmetic operations

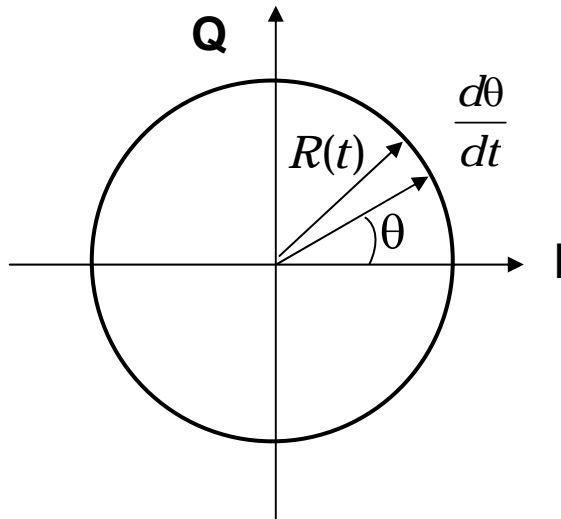
1) AM demodulation

$$\underline{[1 + S(t)] \cdot \exp(j\omega_c t)} \times \underline{\exp(-j\omega_c t)} = 1 + S(t)$$



2) FM demodulation

$$R(t) \exp\left(\Delta j\omega t + jK_d \int m(\tau) d\tau\right)$$



$\Delta\omega$: Frequency offset

$R(t)$: Amplitude variation

$m(\tau)$: Baseband signal to be recovered

$$\theta = \Delta\omega t + K_d \int m(\tau) d\tau$$

$$\frac{d\theta}{dt} = \Delta\omega + K_d m(t)$$

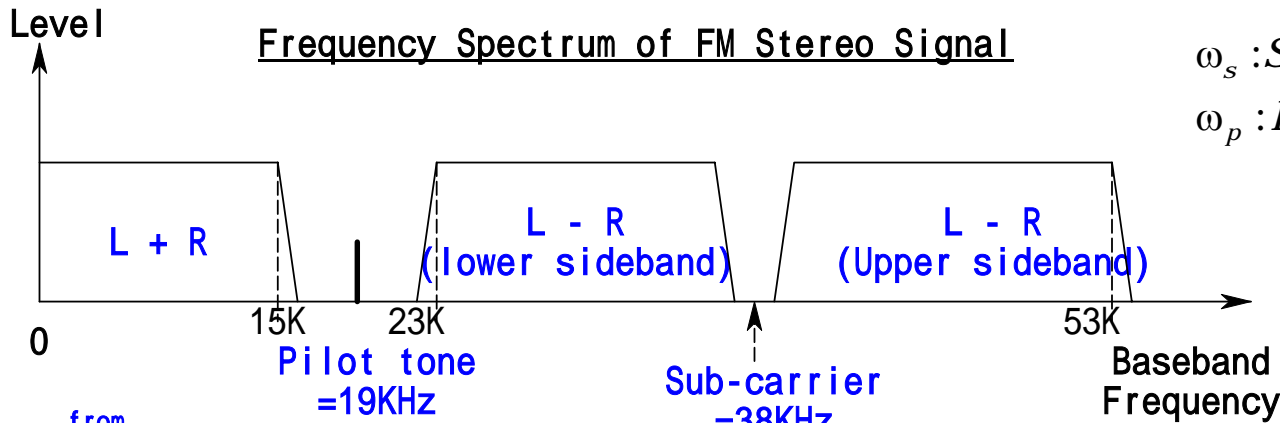
$m(t)$ can be demodulated



Stereo decoder

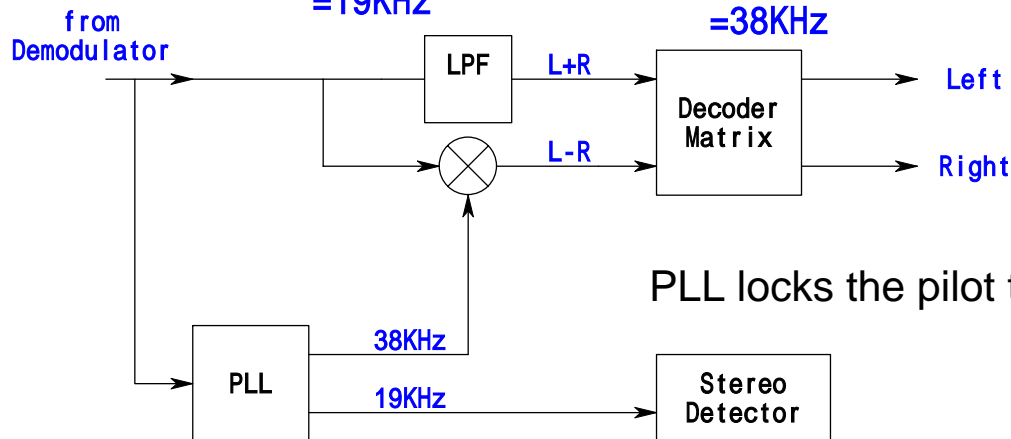
The stereo signal can be reconstructed by numerical PLL, mixer, and filter.

$$S(t) = (L + R) + (L - R)\cos\omega_s t + K\cos\omega_p t$$



ω_s : Sub - carrier = 38KHz

ω_p : Pilot tone = 19KHz



$$(L + R) + (L - R) = 2L$$

$$(L + R) - (L - R) = 2R$$

PLL locks the pilot tone and generates 38KHz for sub-carrier

Image signal can be rejected by using I/Q mixer and phase shift.

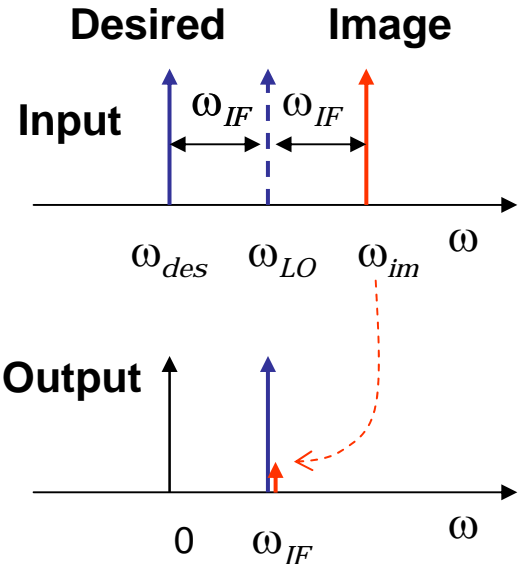
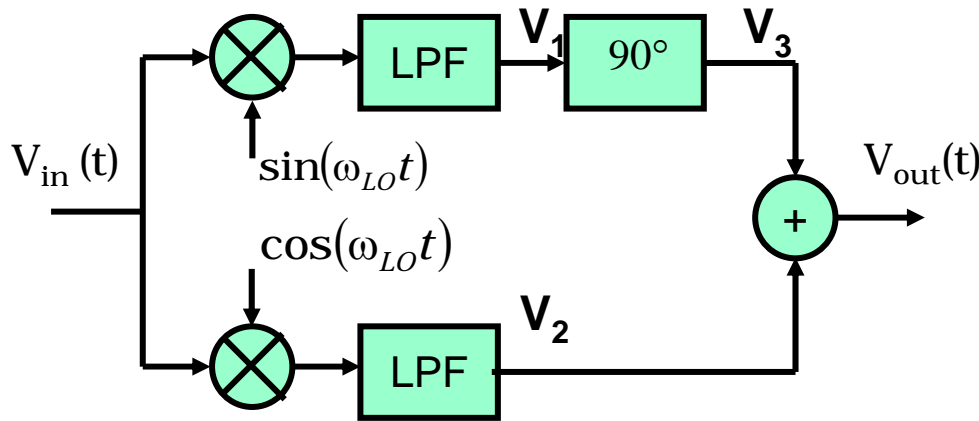


Image rejection mixer

$$V_1(t) = -\frac{V_{des}}{2} \sin(\omega_{des} - \omega_{LO})t + \frac{V_{im}}{2} \sin(\omega_{LO} - \omega_{im})t$$

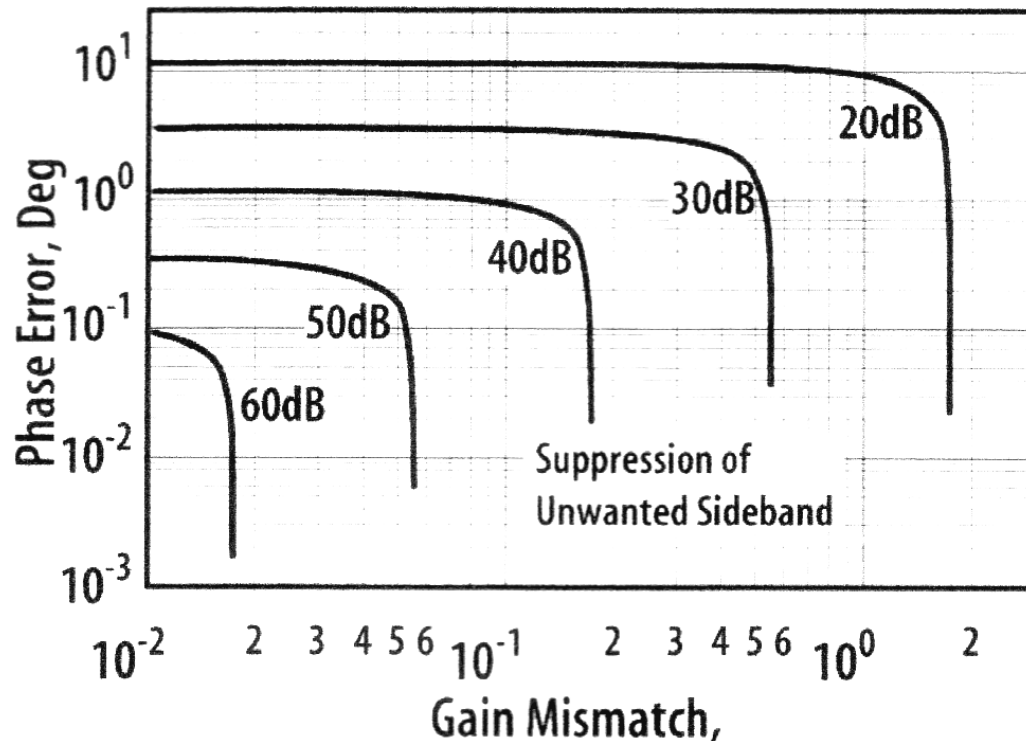
$$V_2(t) = \frac{V_{des}}{2} \cos(\omega_{des} - \omega_{LO})t + \frac{V_{im}}{2} \cos(\omega_{LO} - \omega_{im})t$$

$$V_1(t) \rightarrow 90^\circ \text{ shift} = V_3(t) = \frac{V_{des}}{2} \cos(\omega_{des} - \omega_{LO})t - \frac{V_{im}}{2} \cos(\omega_{LO} - \omega_{im})t$$

$$V_{out}(t) = V_{des} \cos(\omega_{des} - \omega_{LO})t$$

Image is rejected, however,...

0.1 deg and 0.01% are needed for IRR of 60dB



Conventional IRR: 35dB

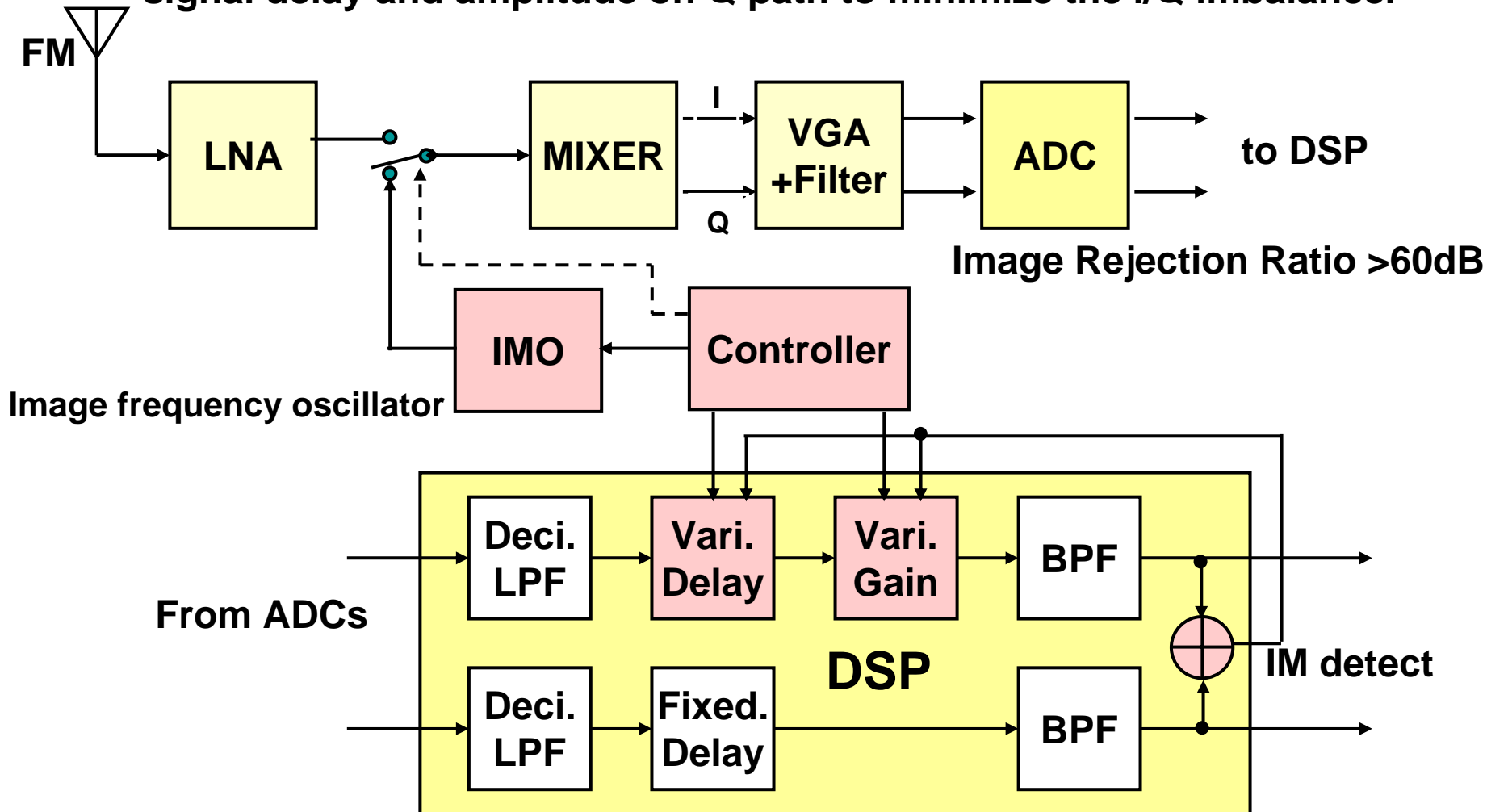
IRR: Image rejection ratio

$$IRR \approx \frac{\left(\frac{\Delta G}{G}\right)^2 + (\Delta\theta)^2}{4}$$

A. Rofougaran, et al.,
IEEE J.S.C. Vol.33, No.4,
April 1998. PP. 515-534.

Image rejection

The dummy image signal is generated by IMO and the controller controls signal delay and amplitude on Q path to minimize the I/Q imbalance.



Impact of components reduction

Reduced components	Reduction ratio	Impact on the Industry
Chip resistor	1 / 10 pcs or less	Components # will be reduced by more than 7 billion pcs per year.
Ceramic capacitor	1 / 10 pcs or less	Components # will be reduced by more than 15 billion pcs per year.
Electrolytic capacitor	1 / 10 ~ 1 / 20 pcs	In AV area estimated 3 billion pcs per year will decrease to less than 500 mil. pcs. Aluminum consumption is expected to decrease by 2 thousand ton per year.
Chip inductor	1 / 2 pcs or less (0 ~ 4pcs)	Components # will be less than half the # of existing pcs, but still some remain.
FM/AM Ceramic filter	0	Estimated 600 mil. pcs per year will be reduced to 0.
Varactor diode	0	In AV area, about 1.5 billion pcs per year will be reduced to 0.
PIN diode	0	In AV area, about 50 mil. pcs per year will be reduced to 0.
Intermediate-frequency transformer	0	About 1 billion pcs per year will be reduced to tens of millions pcs.
Bipolar IC for tuner	Incorporated into Full CMOS	Bipolar IC exclusive for RF is not necessary any more.
Printed board	1 / 6 pcs or less	
Tuner module	Unit manufacturers fix IC directly onto unit base	Tuner makers are not necessary any more.

* Assuming that units manufactured per year are : 100 mil. units for car radios, 80 mil. units for home radios.

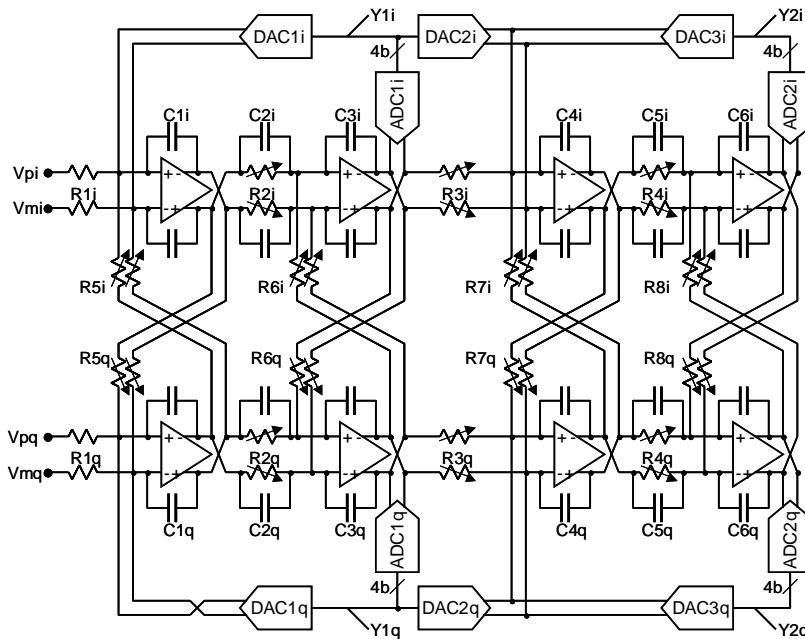
Wide band and high dynamic range delta-sigma ADC is the key for digital centric systems

90nm CMOS, BW=20MHz, DR(=SNR)=77dB, 50mW, FoM=200fJ/conv.

L. J. Breems, et., al.

“A 56mW CT Quadrature Cascaded SD Modulator with 77dB in a Near aero-IF 20MHz Band.

ISSCC 2007, pp. 238-239.



Technology	90nm CMOS, 1P6M
Supply voltage	1.2V
Architecture	CT quadrature cascaded $\Sigma\Delta$ modulator (2-2, 4b)
Sampling frequency	340MHz
Bandwidth	20MHz @ 10.5MHz IF
Max. input voltage	1Vp (differential)
Dynamic range*	77dB (97dB @ 200kHz, 115dB @ 3kHz)
Peak SNR / SNDR*	71dB / 69dB
Image rejection	>55dB (for -1MHz input tone)
Active chip area	0.5mm ²
Power consumption	50mW (analog), 6mW (digital)
Figure-of-merit (FOM)	0.2pJ/conv. (FOM=P/(2 ^{enob} *2*BW))

(*1MHz input signal, signal bandwidth is 20MHz)

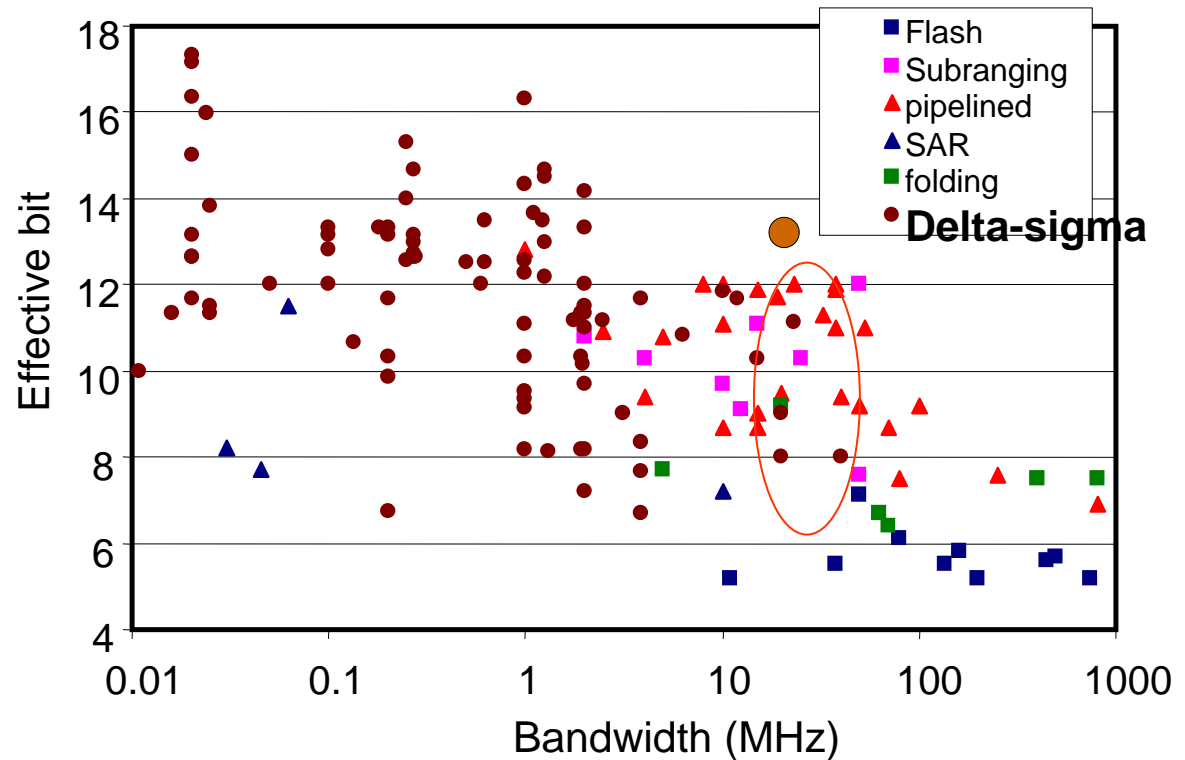
The bandwidth of sigma-delta ADCs has been increased up to 20MHz with effective resolution of about 12 bit.

Nyquist ADC:

$$SNR \propto CV_{sig}^2$$

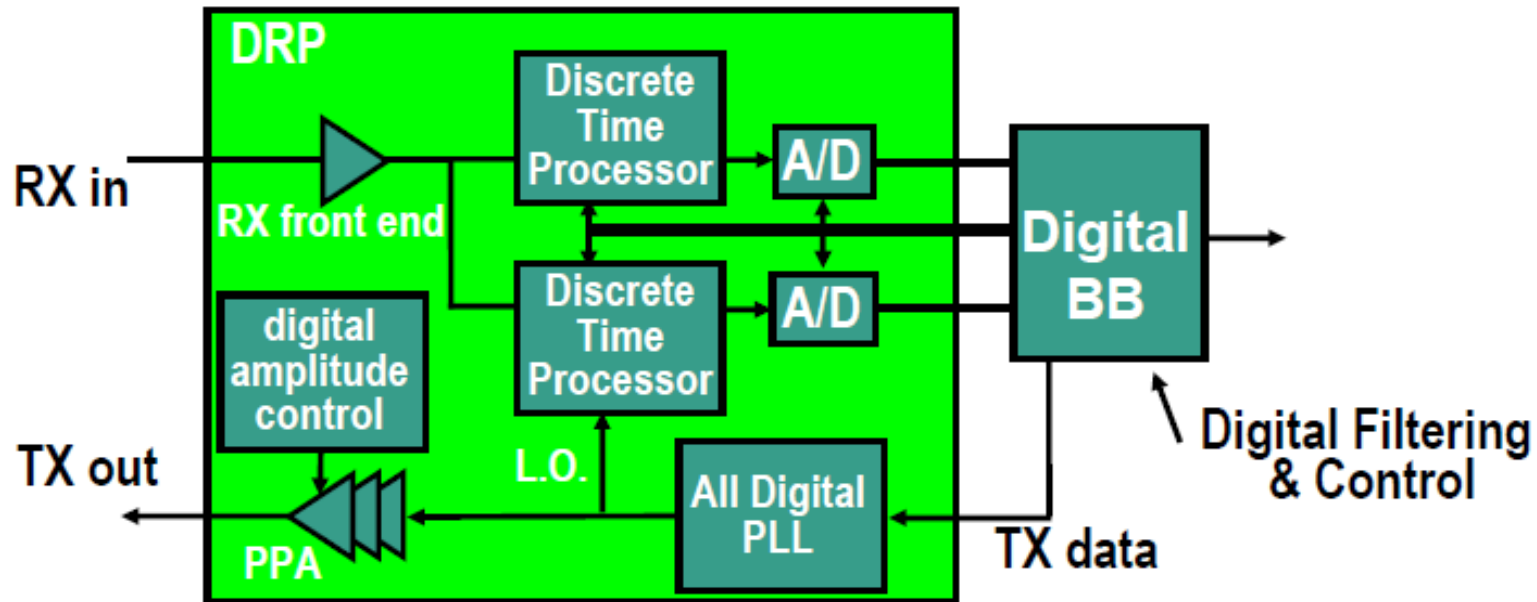
Delta-sigma ADC:

$$SNR \propto CV_{sig}^2 \cdot M^\alpha$$

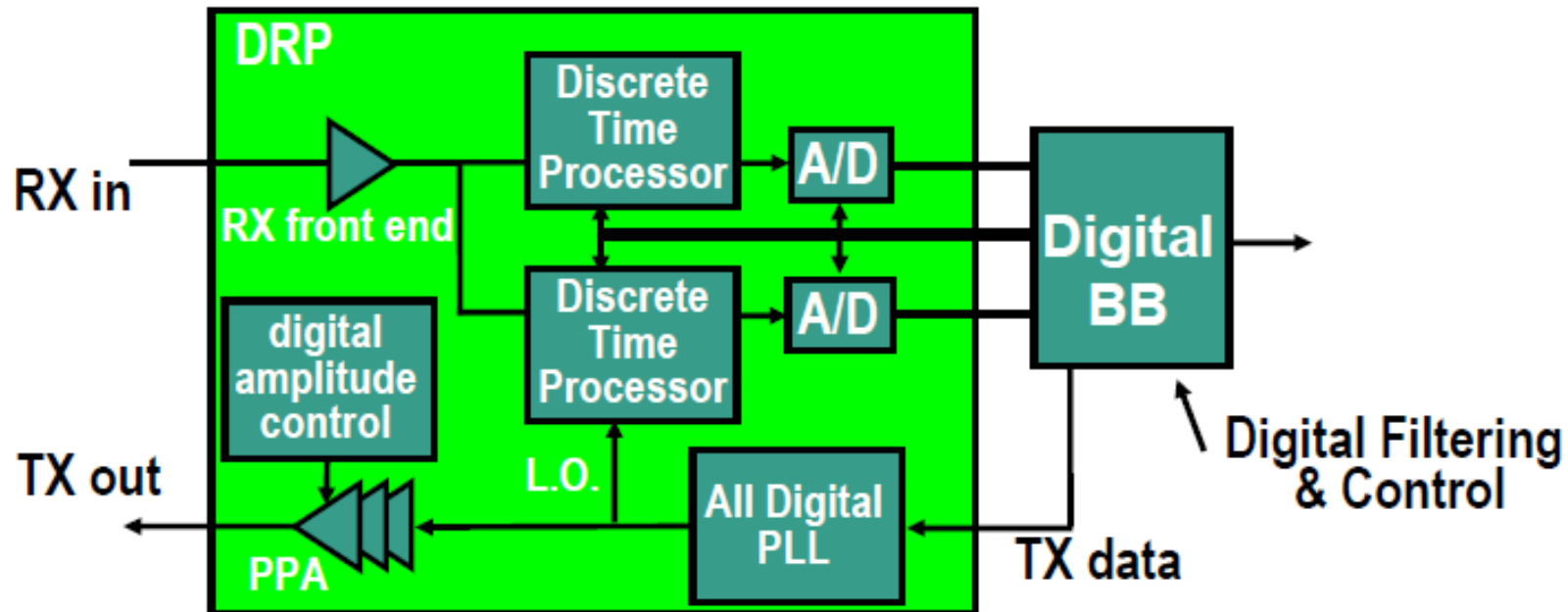


DRP: Digital RF Processing

Courtesy Dr. R. B. Staszewski, TI

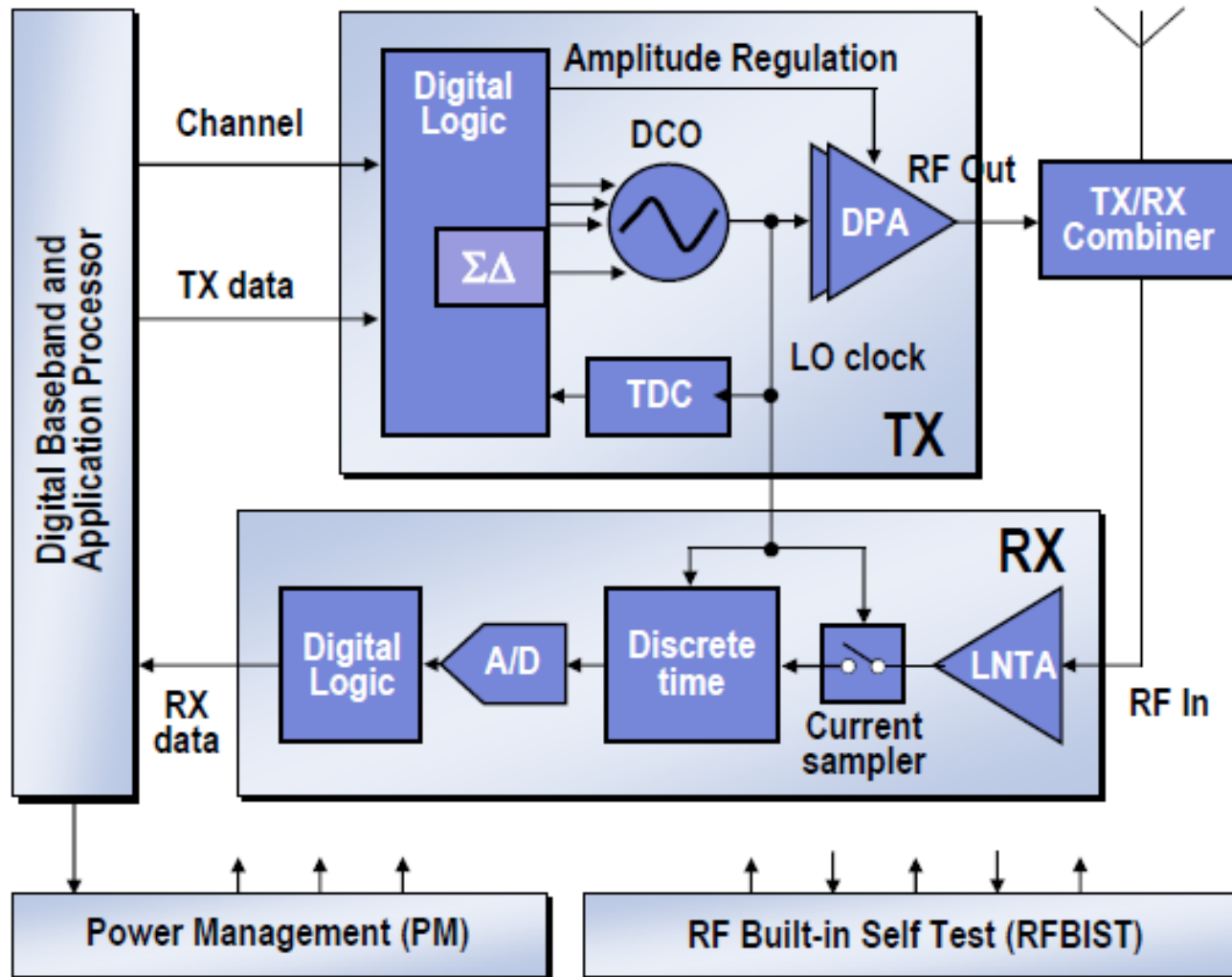


- **Minimize analog and RF circuitry**
 - Self-calibrate remaining analog (with dedicated processor)
 - Relax passive requirements as much as possible
- **Digital approach speeds debug and development**
- **Self-test and calibration made possible**
- **Production yield dominated by silicon defect density**



- **Move functions to domains of CMOS-process strengths**
 - Operate in fine time resolution, avoid fine voltage resolution
 - Inductor area could be equal to ~100K gates (use digital!)
 - Use switched cap techniques – excellent matching in DSM CMOS (not sensitive to process variations)
 - Logic and switched cap circuits can work well at low voltage

DRP Architecture



0.2, 1.25, 2.5, 5,
10, 15, 20MHz BW

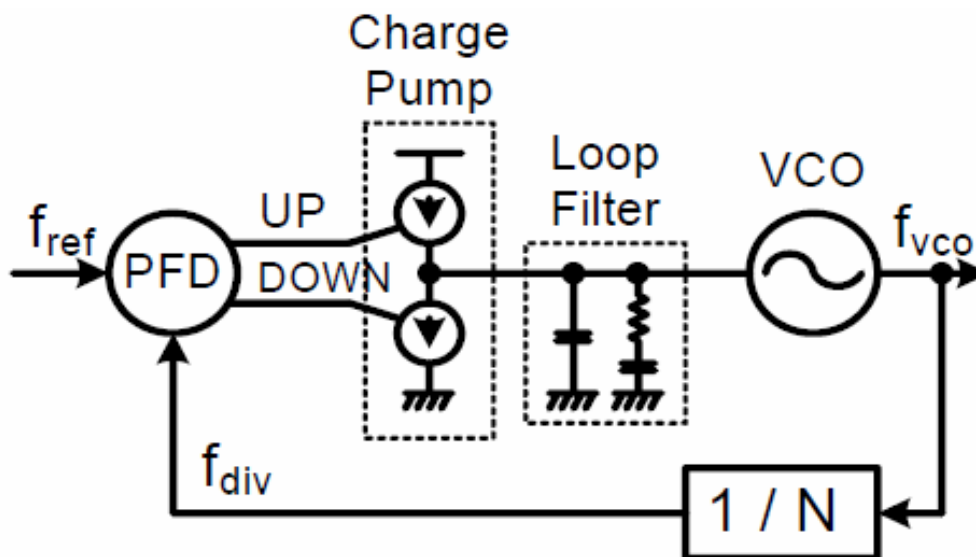
450, 800, 900,
1800, 1900, 2100,
2500, 3400MHz
Transmission bands

GMSK, QPSK,
8-PSK, 16QAM,
64QAM Modulation

TDMA, FDMA,
CDMA, OFDMA,
IFDMA schemes

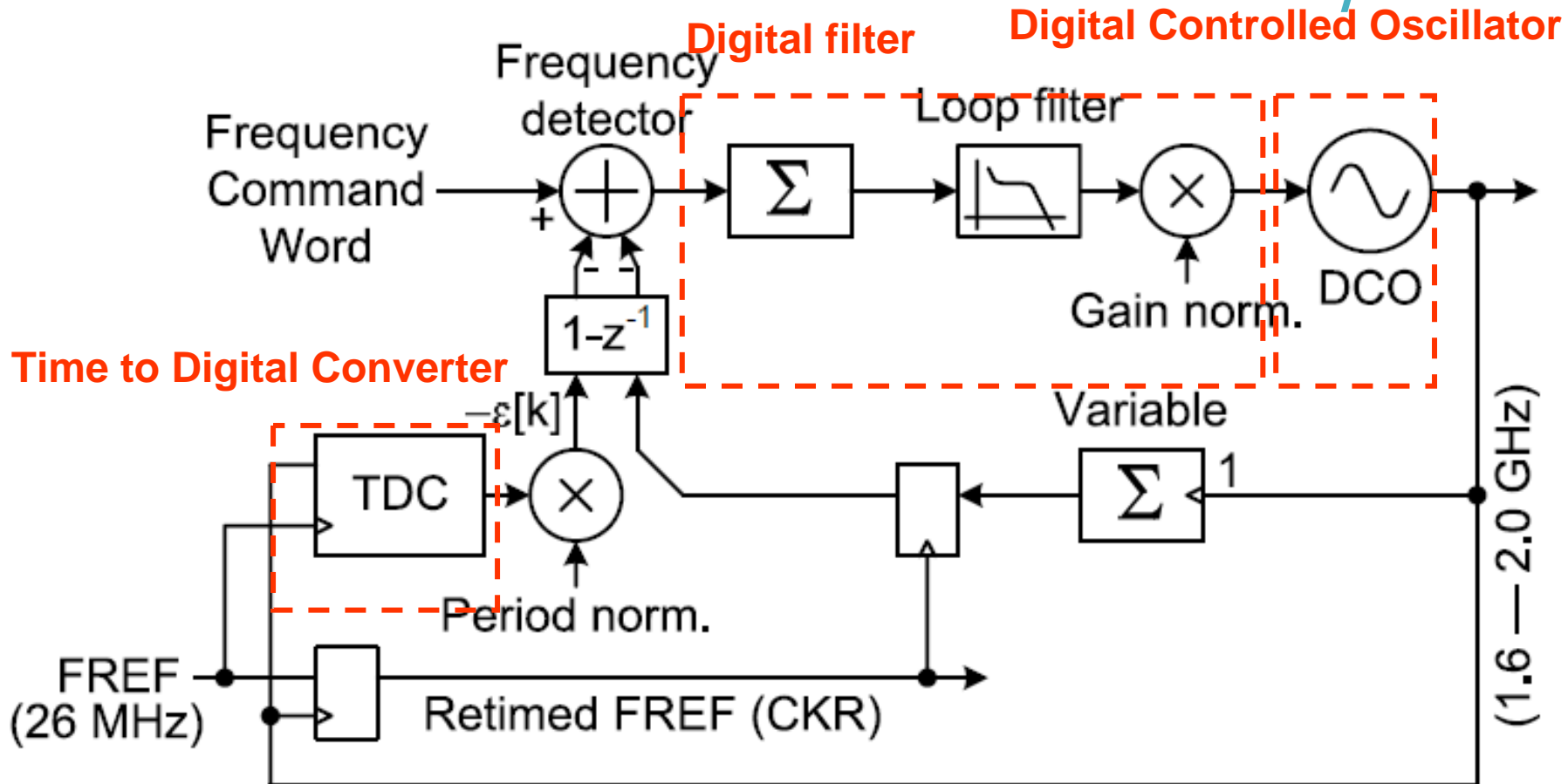
Looks almost
like SDR!!

Performance of conventional PLL will degrade along with technology scaling. Functions is not sufficient for future systems.



- Many analog functions = multiple noise sources
- Varactors in VCO are sensitive (high tuning factor, i.e. KVCO)
- Loop filter may be large, leaky capacitors (for open loop “freeze”), variances in passives...
- Hard to calibrate
- Lock times can be long ($>100\mu\text{sec}$)

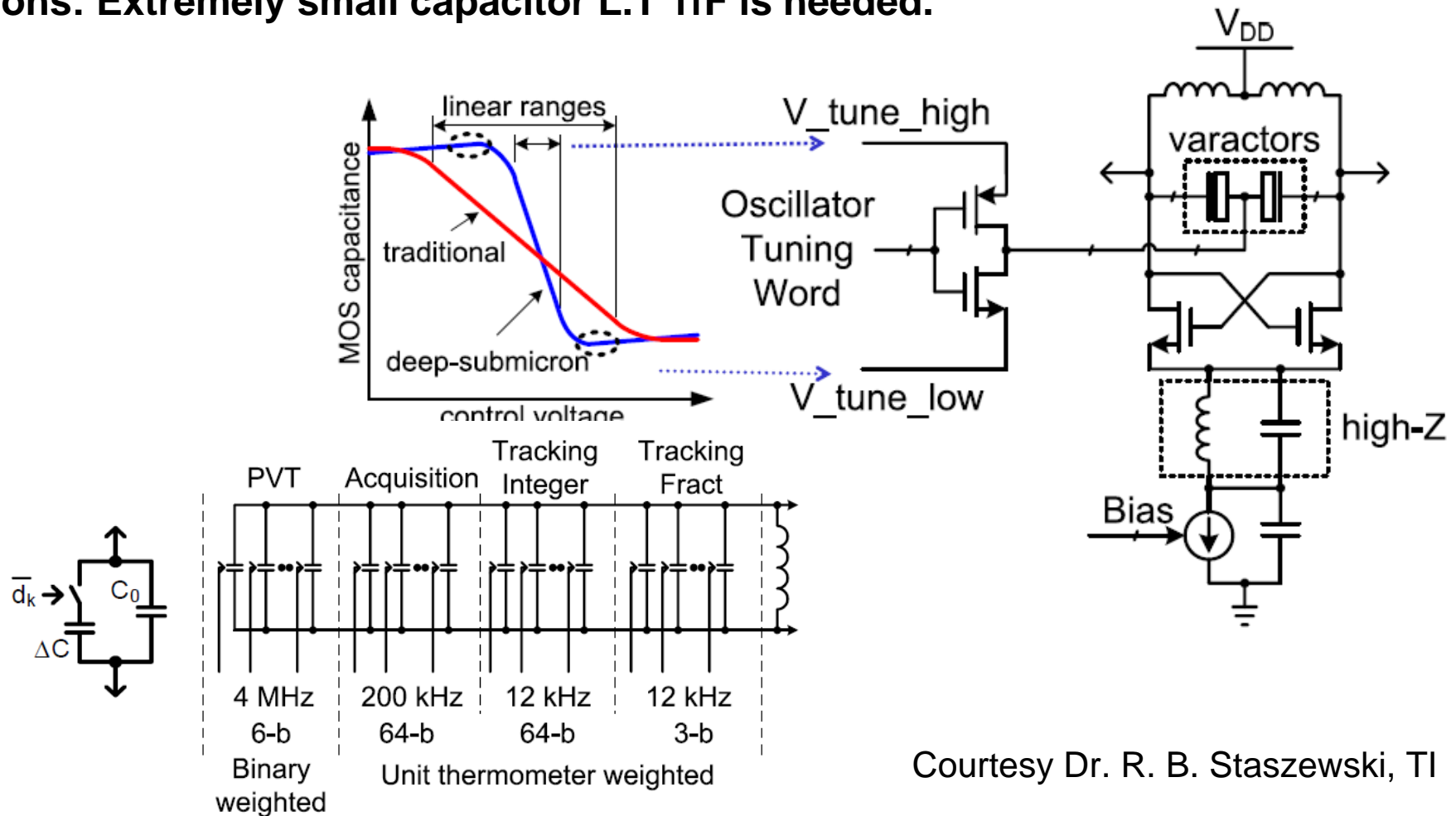
All-Digital PLL



References [2], [3] - R. Bogdan Staszewski et al.

Digitally-controlled oscillator

Pros: Small effect to AM/PM conversion and noise on control voltage.
Cons: Extremely small capacitor L.T 1fF is needed.

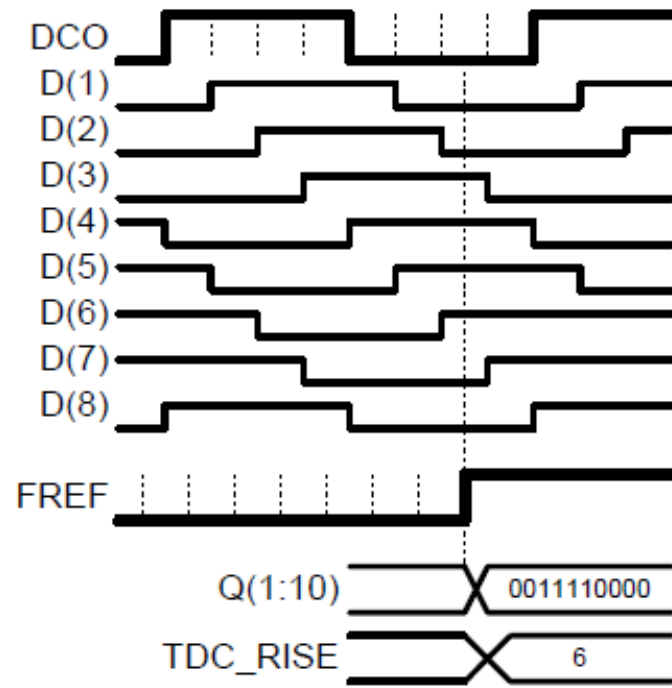
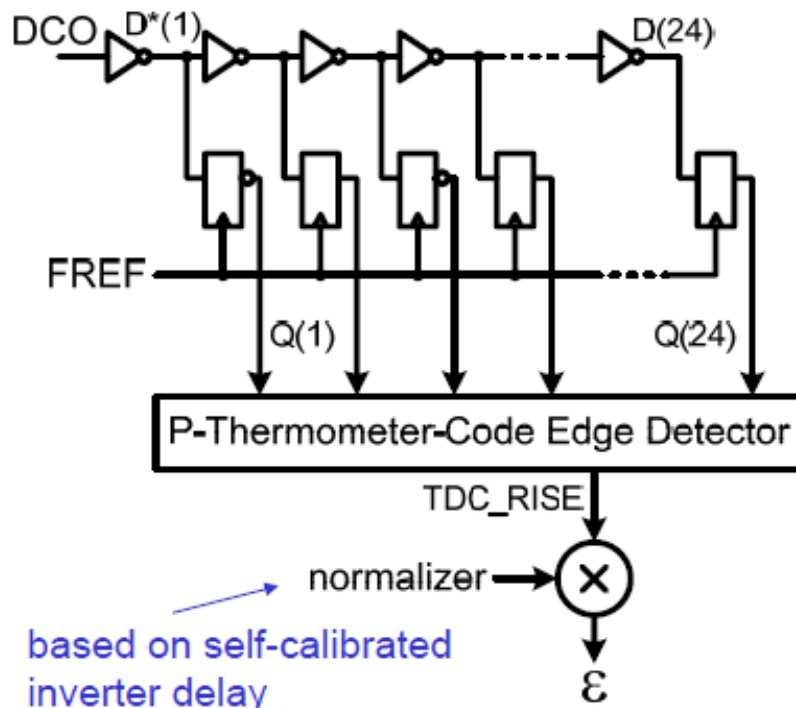


Courtesy Dr. R. B. Staszewski, TI

High-speed dithering and dynamic element matching are used to achieve high resolution (LSB = ~1.5Hz).

Issue: more small delay will be required.

- ◆ Quantized phase detector with resolution of about 20 ps
- ◆ DCO clock passes through the inverter chain
- ◆ Delayed outputs are sampled by FREF

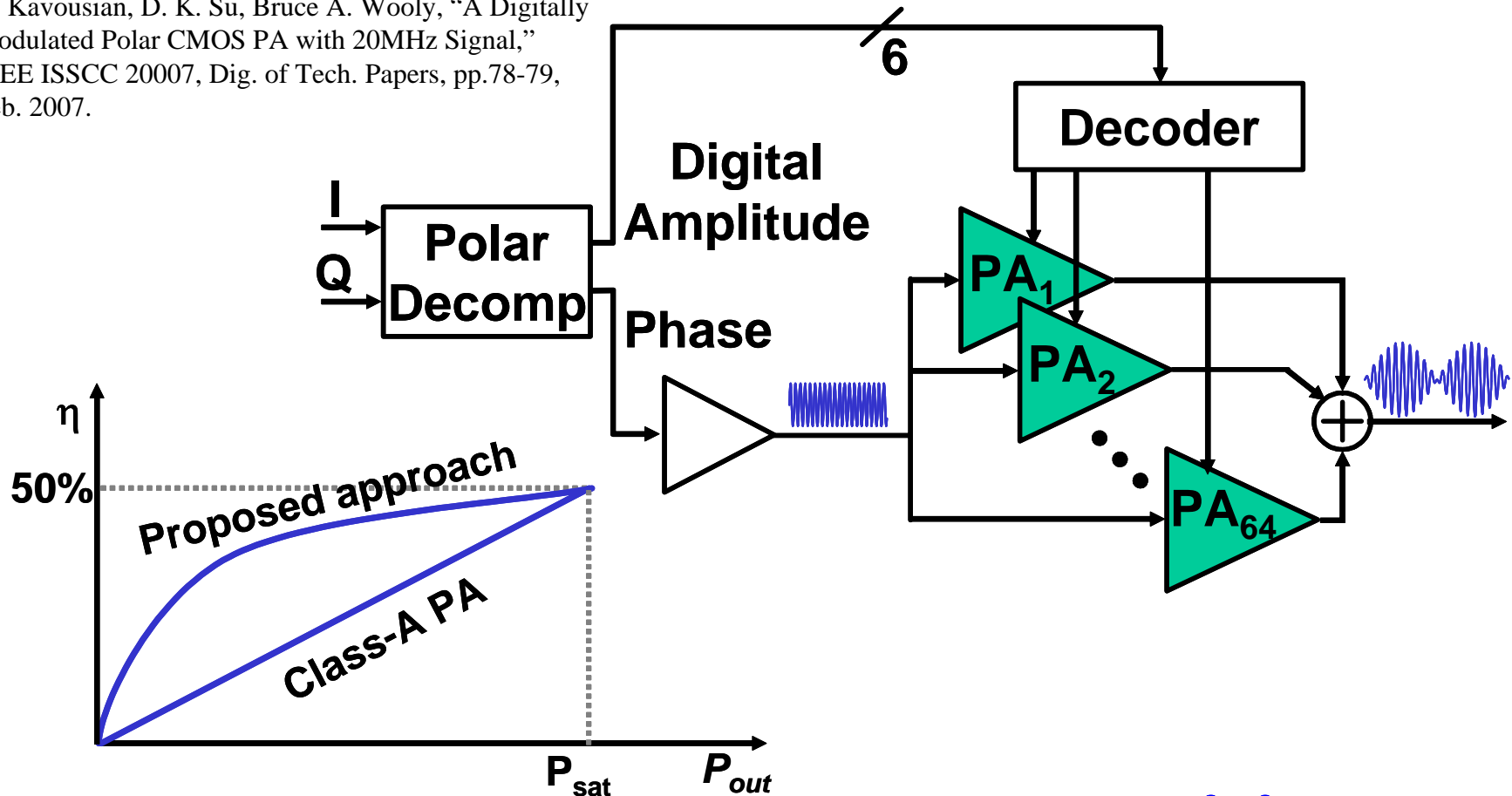


Digital polar modulation

Amplitude modulation has been realized by RF-DAC.

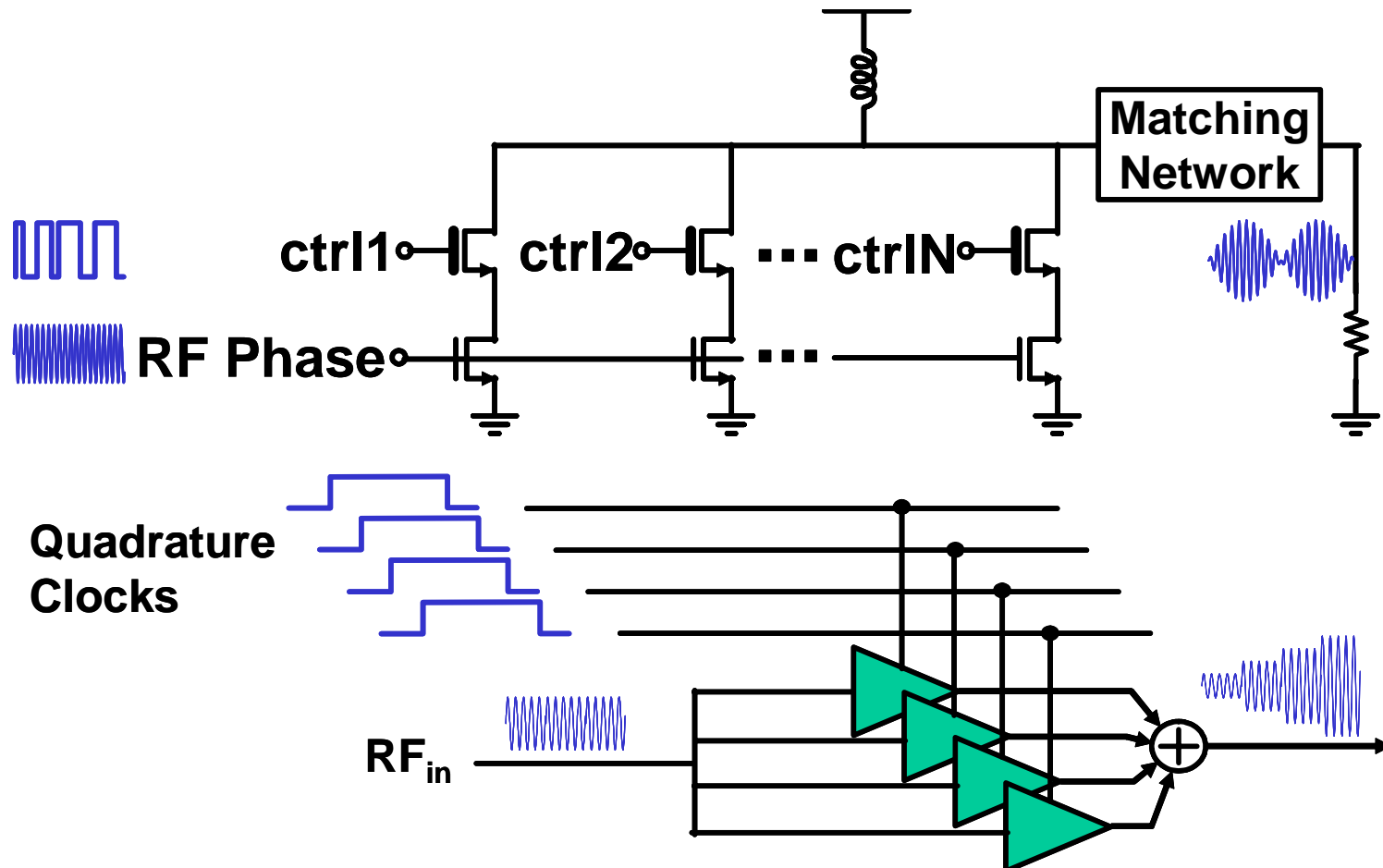
PA consists of DAC.

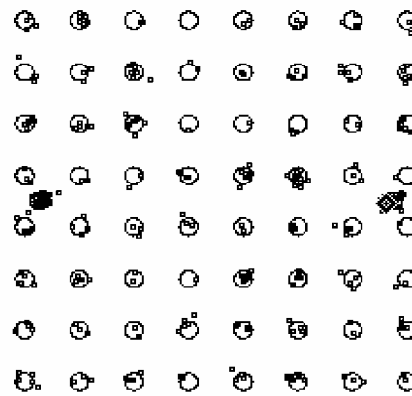
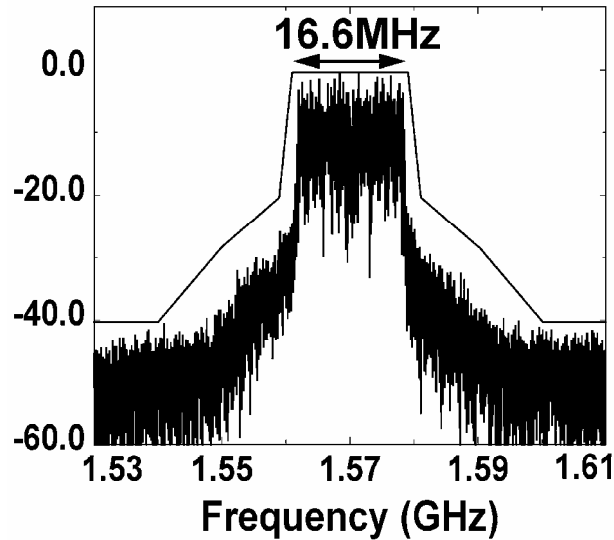
A. Kavousian, D. K. Su, Bruce A. Wooly, "A Digitally Modulated Polar CMOS PA with 20MHz Signal," IEEE ISSCC 2007, Dig. of Tech. Papers, pp.78-79, Feb. 2007.



PA using DAC

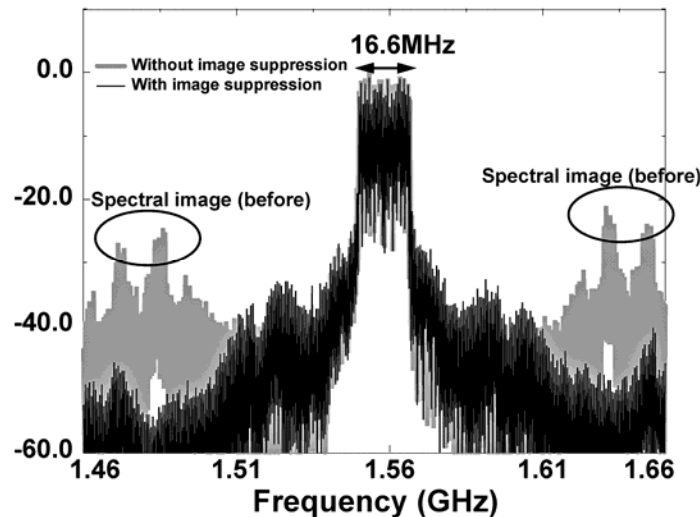
64 small PAs are controlled by digital BB signal.





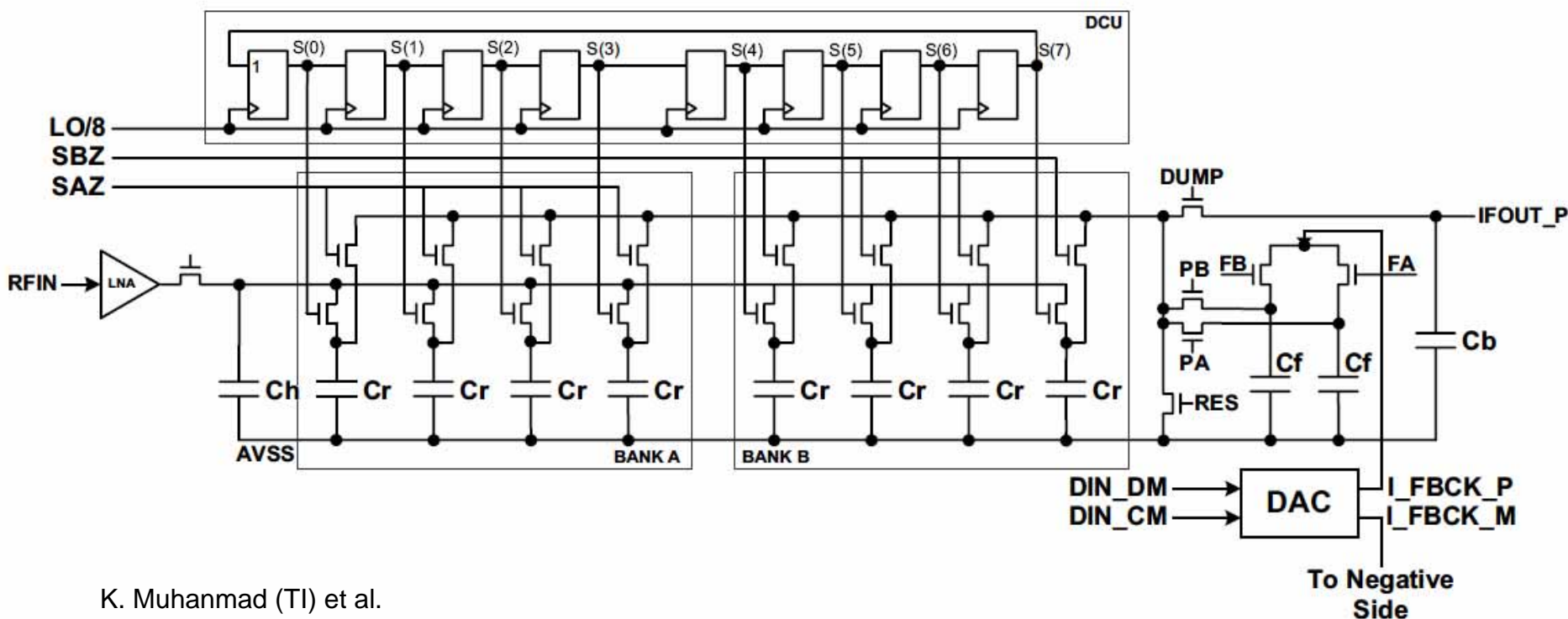
Po=13dBm
PAE=7.2%
BW=20MHz

EVM = -26.8dB



Technology	0.18μm CMOS, 2P5M
Supply Voltage	
Digital Hardware	1.8V
Driver Stage	2.2V
Output Stage	1.7V
Linear 64 QAM OFDM Output Power	14.7dBm 13.6dBm (balun included)
EVM for 64 QAM OFDM	-26.8dB
Dissipated Power	
Output Stage	247mW
Driver Stage	66mW
Digital	3.4mW
PAE (for 64QAM OFDM)	8.9% 6.7% (baluns included)
Center Frequency	1.56GHz
Total Chip Area	1.8mm ²

標本化回路はそれ自体ミキサー作用を持つが、容量アレーを用いて演算を行うことによりフィルター特性を持たせることができる。(離散時間信号処理のRF応用)
スイッチと容量という準受動回路で実現できるので、微細化に向いており、低電力である。



K. Muhanmad (TI) et al.

"All-Digital TX Frequency Synthesizer and Discrete-Time Receiver for Bluetooth Radio in 130-nm CMOS"

(JSSC Vol.39, No.12, pp. 2278-2291, Dec. 2004)

- LOクロックN回の移動平均

$$W_i = \sum_{l=0}^{N-1} u_{i-l}$$

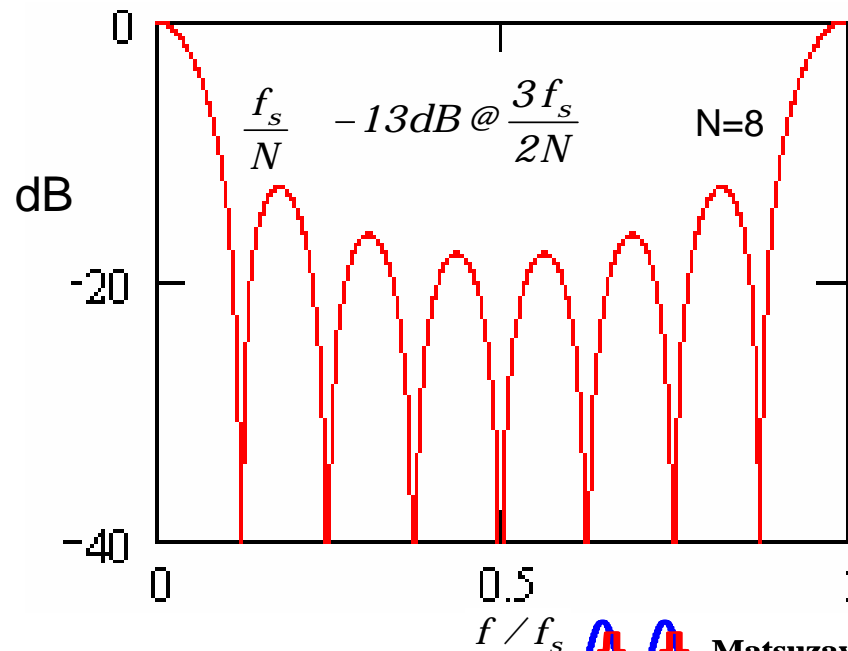
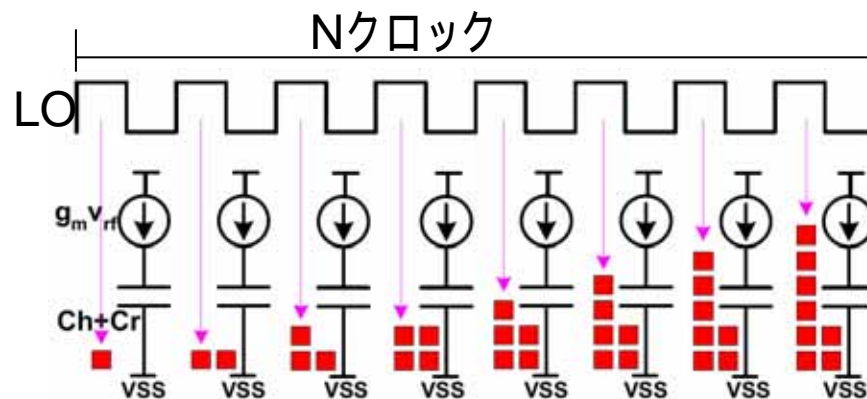
u_i : i番目にサンプリングされた電荷

w_i : Nクロックの間に蓄積された電荷

$$w_i = \sum_{l=0}^{N-1} u_{i-l}$$

$$\rightarrow W(Z) = \frac{1 - Z^{-N}}{1 - Z^{-1}} U(Z)$$

$$\rightarrow |F_{1stSinc}(\omega)| = \left| \frac{\sin\left(N\pi \frac{f}{f_s}\right)}{\sin\left(\pi \frac{f}{f_s}\right)} \right|$$



- 電荷が C_h と C_r に分割して蓄積される

$$s_j = as_{j-1} + w_j \xrightarrow{i=Nj} s_i = as_{i-N} + w_i$$

$$a = \frac{C_h}{C_h + C_r}$$

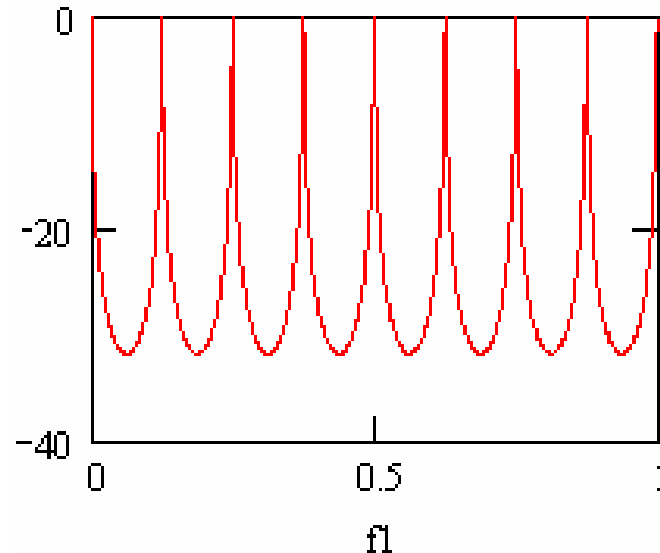
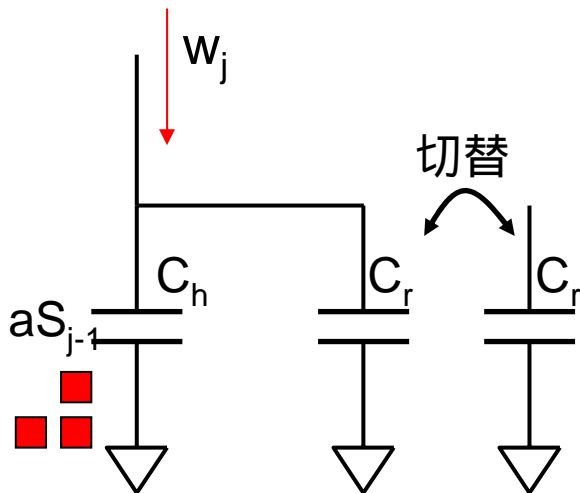
$$s_i = as_{i-N} + w_i \rightarrow S(Z) = \frac{W(Z)}{1 - aZ^{-N}}$$

$$\rightarrow |F_{1stIIR}(f / f_s)| = \frac{1}{\sqrt{1 + a^2 - 2a \cos\left(N2\pi \frac{f}{f_s}\right)}}$$

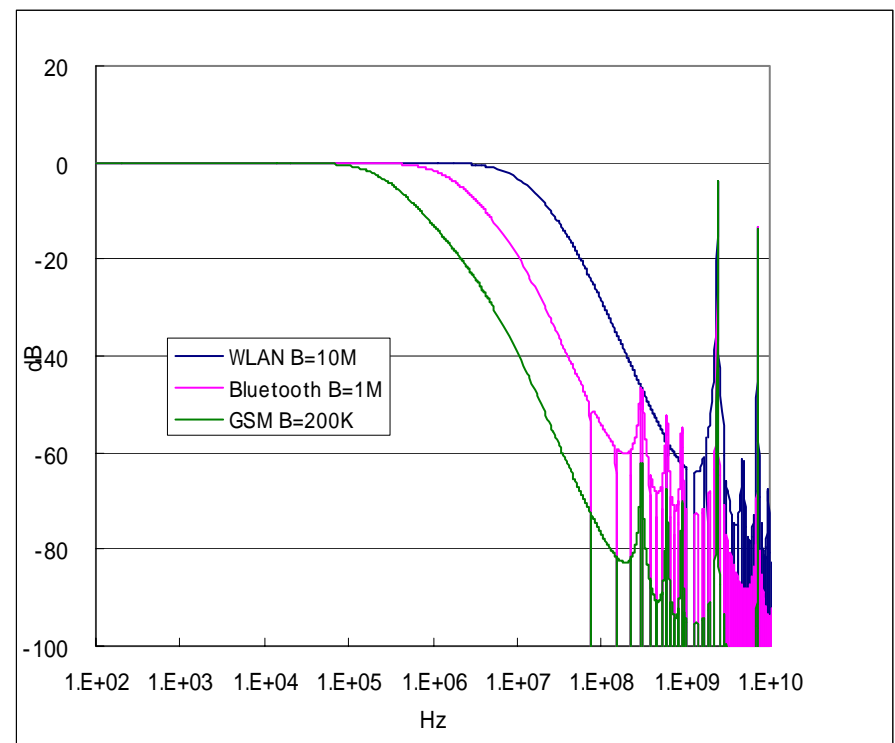
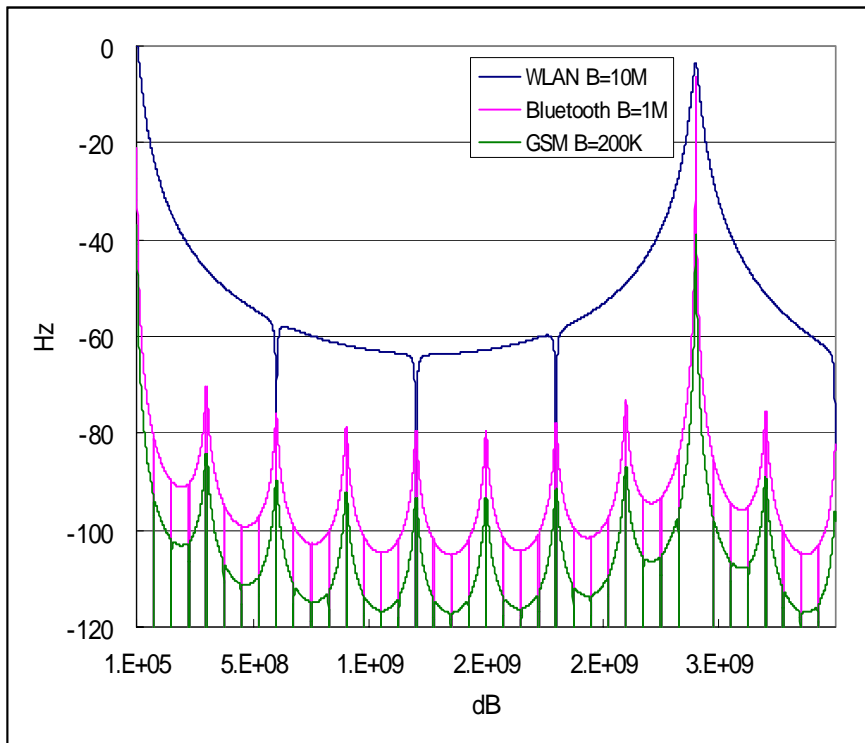
as_{j-1} : $j-1$ のとき C_h に蓄積された電荷

w_j : j のとき C_h と C_r 注入された電荷

s_j : j で C_h と C_r に蓄積されている電荷の合計



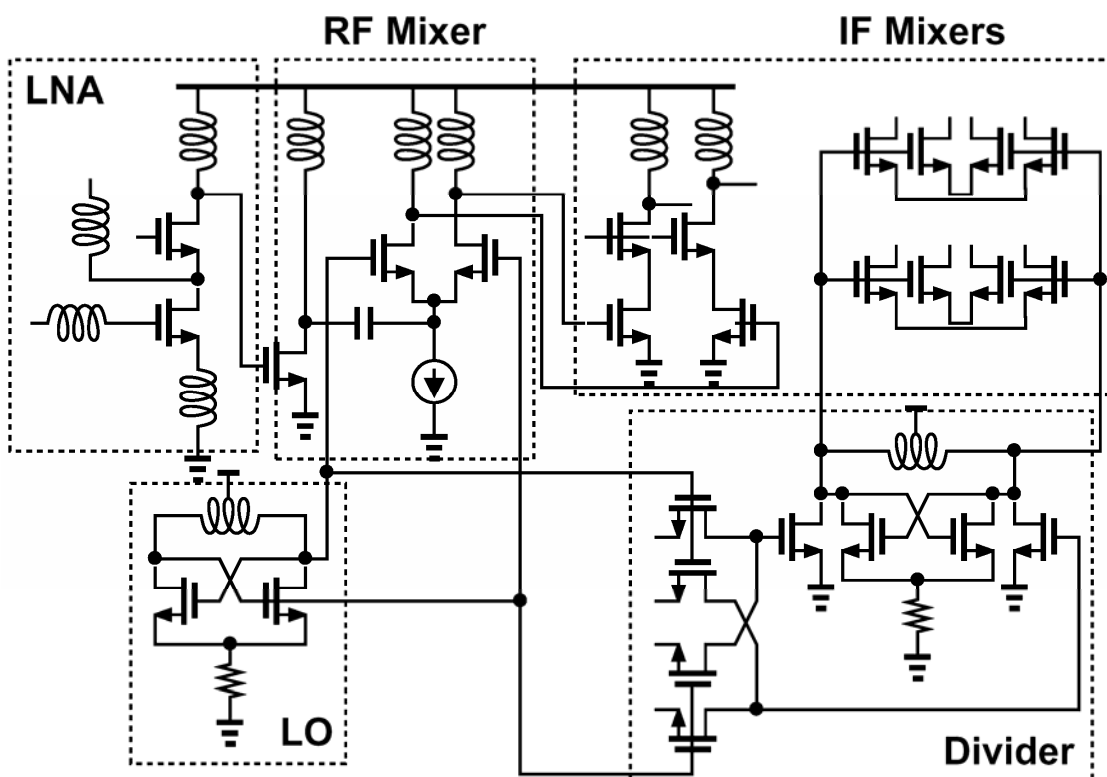
容量比や平均化回数などを変えることによりフィルター特性を可変にできる



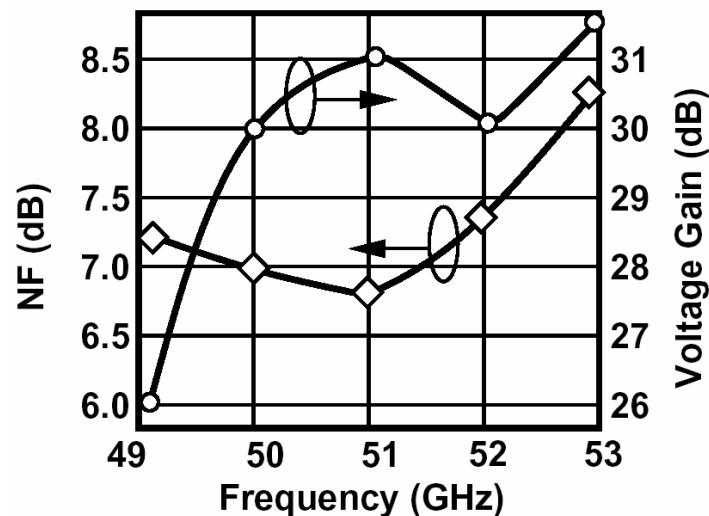
mm-wave SoCs

60GHz ミリ波CMOSレシーバー 1

90nm CMOSを用いて60GHzのレシーバーを実現



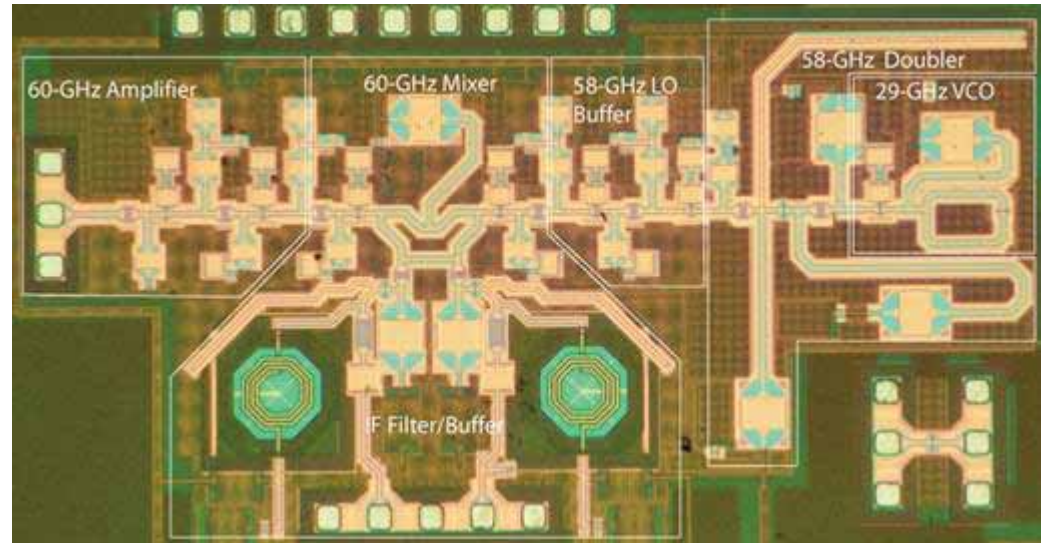
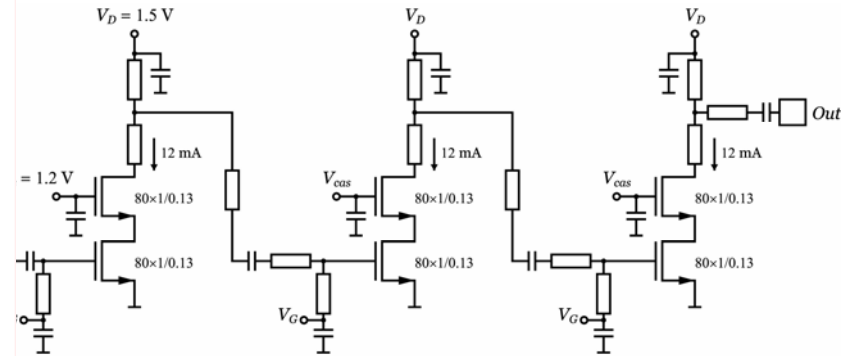
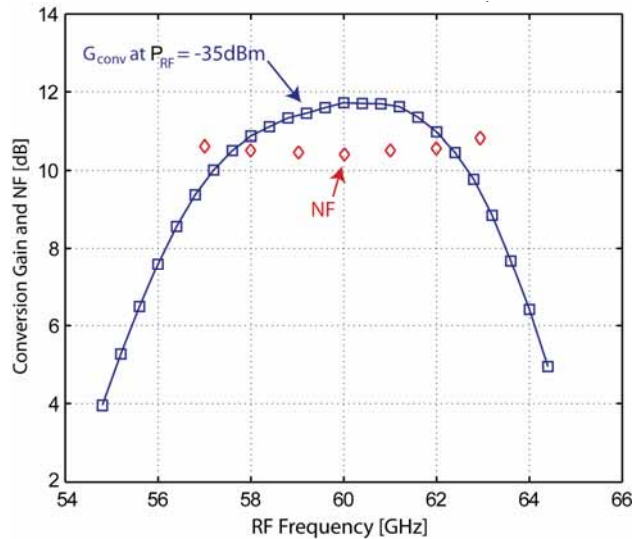
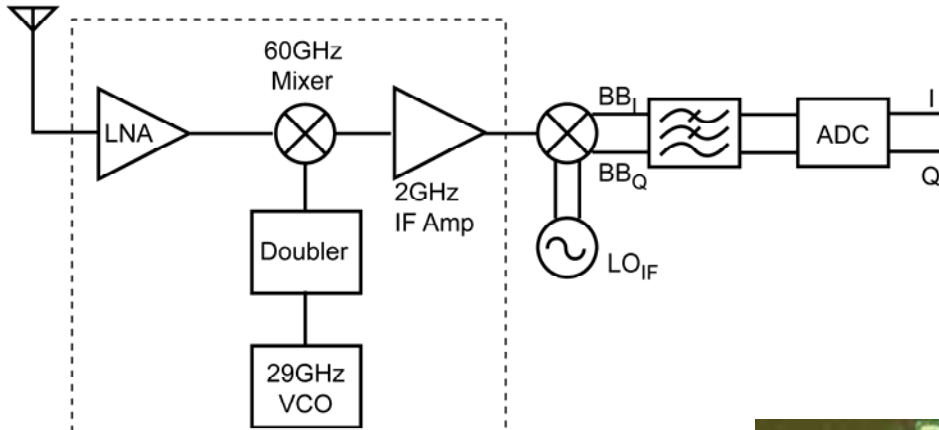
B. Razavi "A mm-Wave CMOS Heterodyne Receiver with On-Chip LO and Driver,"
IEEE ISSCC 2007, Dig. of Tech. Papers, pp.188-189, Feb. 2007.



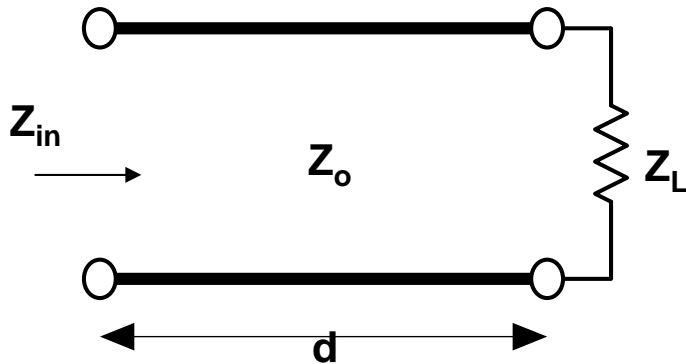
60GHz ミリ波CMOSレシーバー 2

0.13um CMOSを用いても60GHzのレシーバーが実現できる

S. Emami, C. H. Doan, A. M. Niknejad, R. W. Broderson, "A Highly Integrated 60GHz CMOS Front-End Receiver," IEEE ISSCC 2007, Dig. of Tech. Papers, pp.180-191, Feb. 2007.



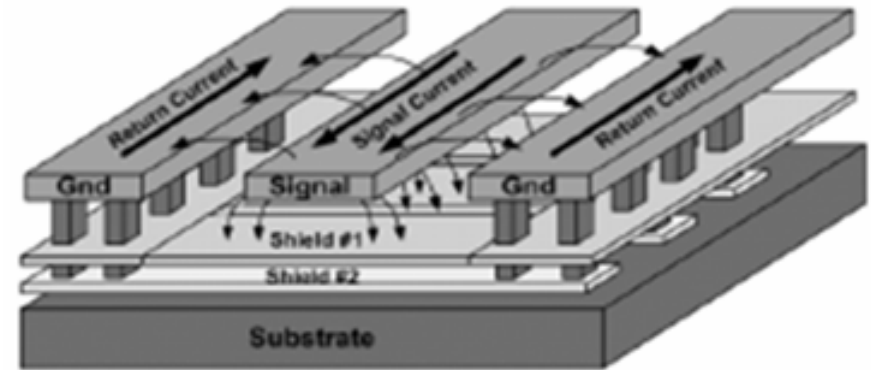
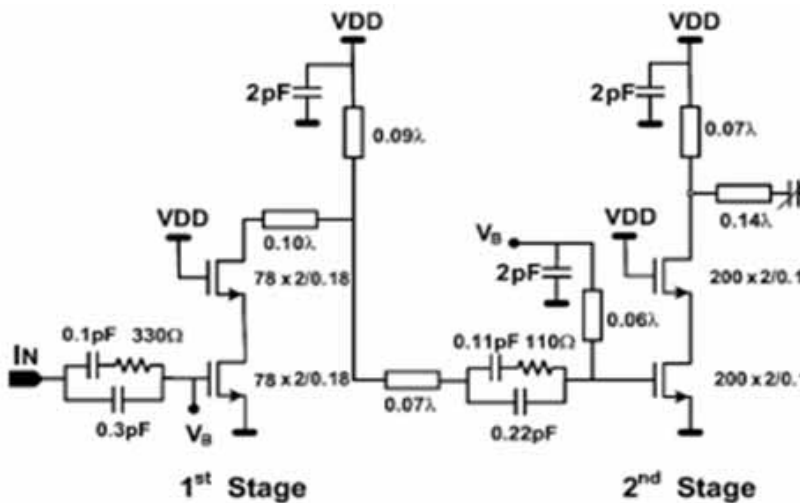
ミリ波では波長が短いためトランスミッションラインが使用できる。
インピーダンス整合や共振器、発振器として使用できる。



$$Z_{in} = Z_0 \frac{Z_L + jZ_0 \tan \beta d}{Z_0 + jZ_L \tan \beta d}$$

resonator

$$Z_{in} \left(\frac{\lambda}{4} \right) = \frac{Z_0^2}{Z_L} \quad Z_{in} \left(\frac{\lambda}{4} \right) = \infty \text{ when } Z_L = 0$$



Coplanar transmission line

ミリ波では波長が数mmになるので、チップ上にアンテナを集積することが可能

給電位相の変化により電子的にビームフォーミング可能

オンチップ上に4つのアンテナを配置

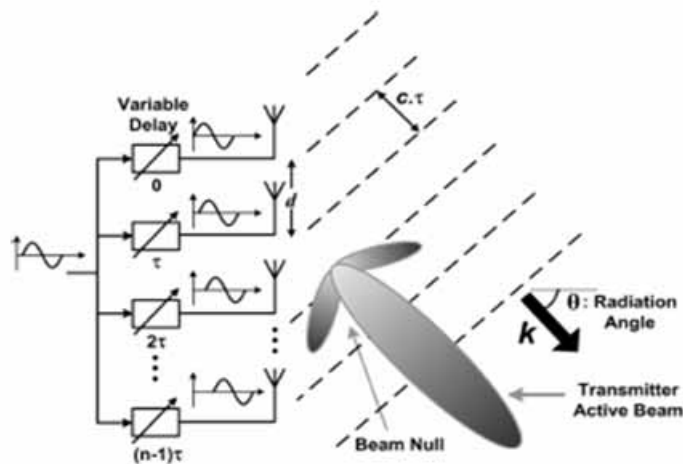
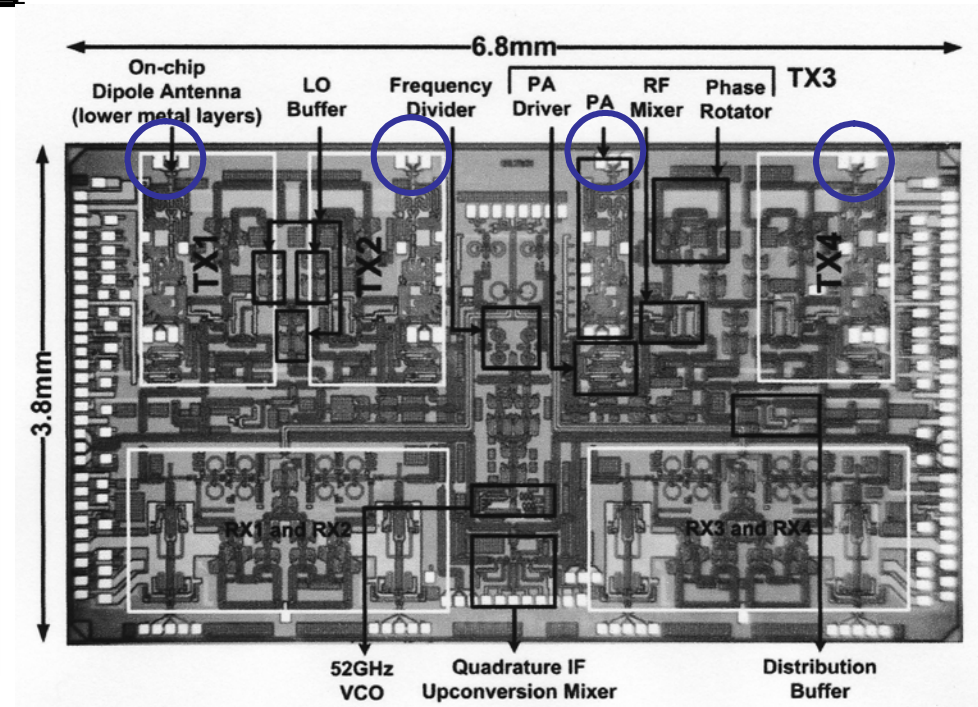


Fig. 1. n -element phased-array transmitter.



A. Natarajan, et. al., IEEE, Journal of Solid-State Circuits, Vol. 40, No. 12, pp. 2502-2514, Dec. 2005.

A. Natarajan, et. al., IEEE, Journal of Solid-State Circuits, Vol. 41, No. 12, pp. 2807-2819, Dec. 2006.

ビームフォーミングは信号強度を上げ、伝送レートを速くするためにも有効

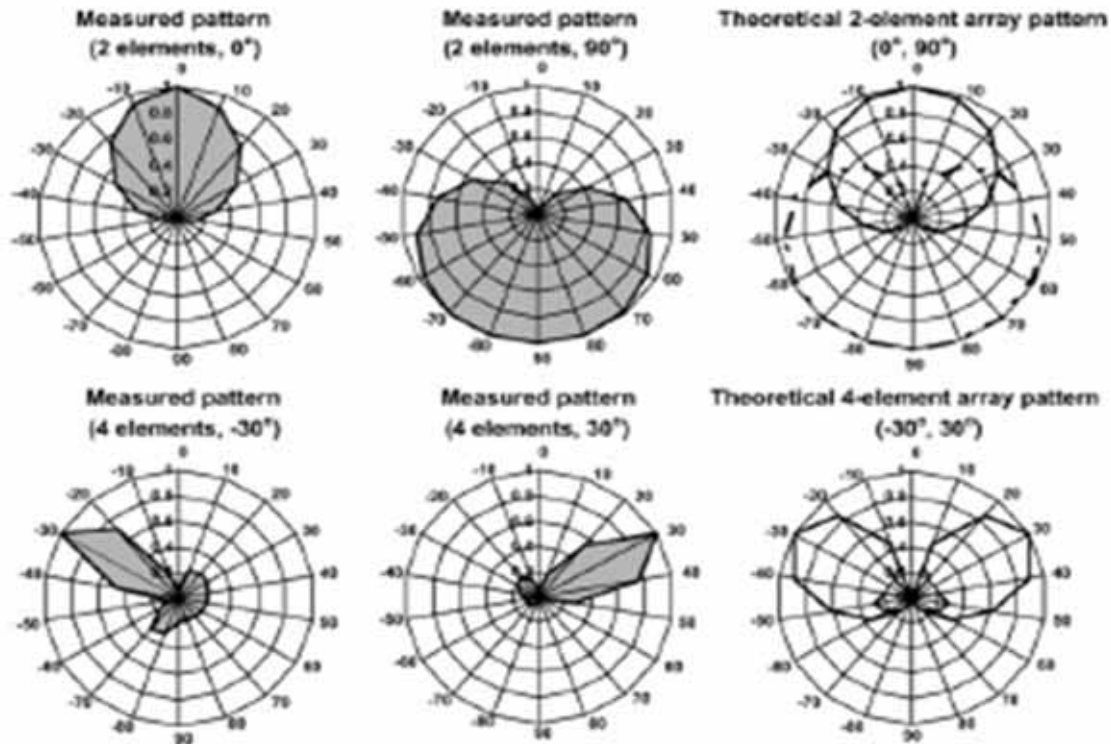


Fig. 21. Comparison of theoretical and measured array pattern with two elements and with four elements active.

77GHzのミリ波トランシーバ: オンチップアンテナとレンズを集積

10.1 A 77GHz 4-Element Phased Array Receiver with On-Chip Dipole Antennas in Silicon

0.13um SiGe-CMOS

A. Babakhani, X. Guan, A. Komijani, A. Natarajan, A. Hajimiri

California Institute of Technology, Pasadena, CA

IEEE ISSCC 2006, Dig. Technical Papers, pp.180-181.

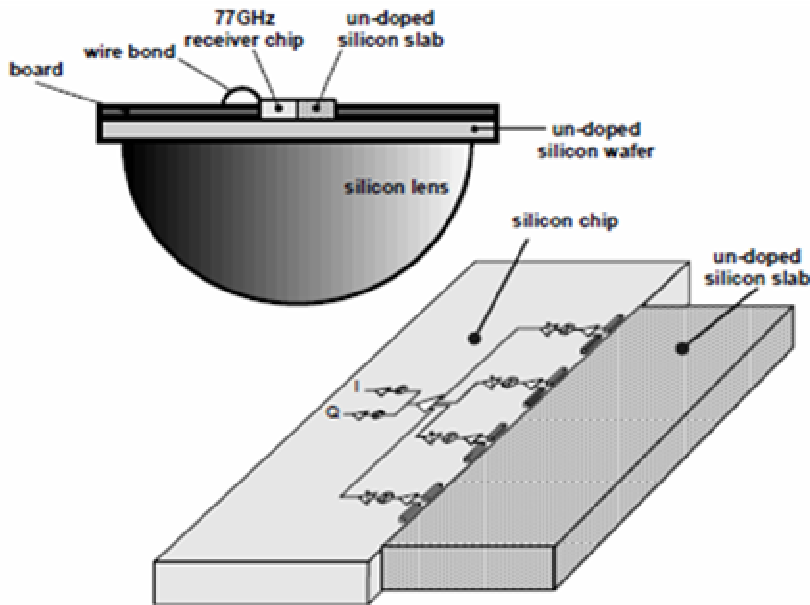


Figure 10.1.1: Chip, board, and lens antenna setup configuration.

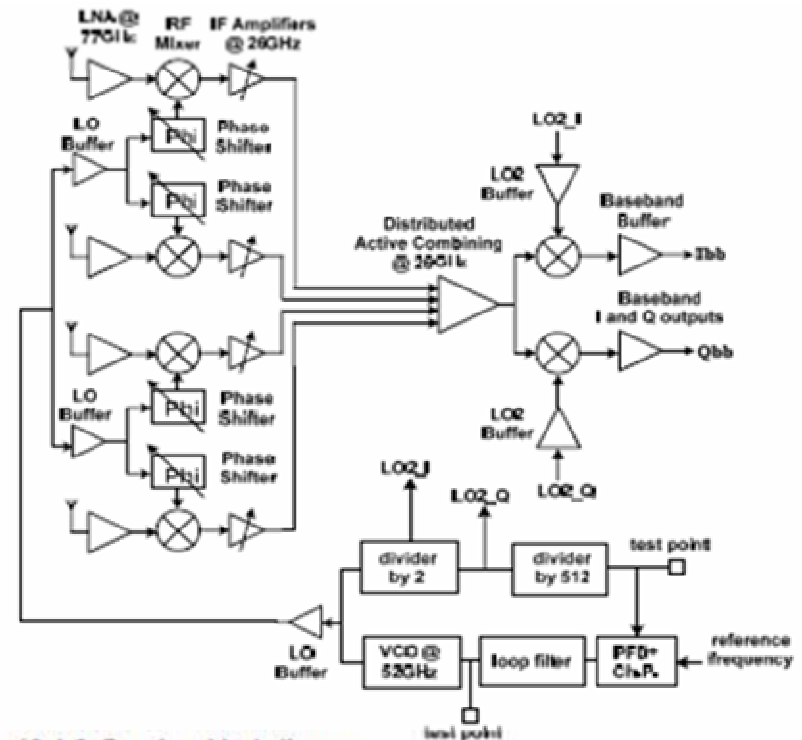


Figure 10.1.3: Receiver block diagram.

レンズを用いることにより10数dBの感度アップ

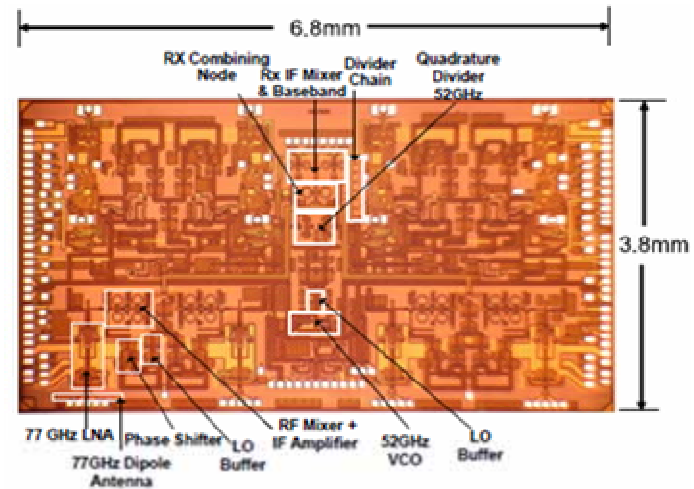
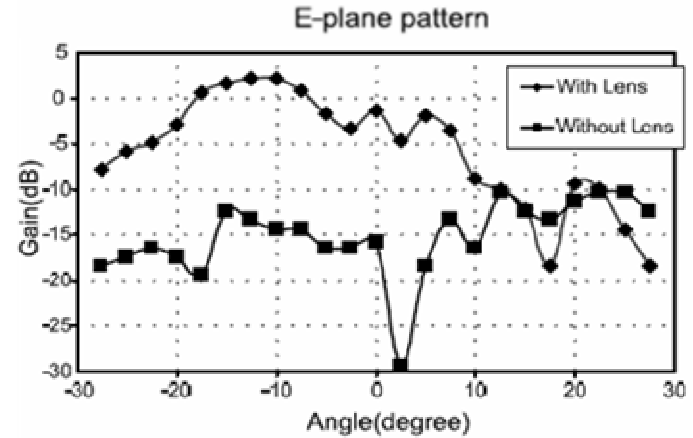
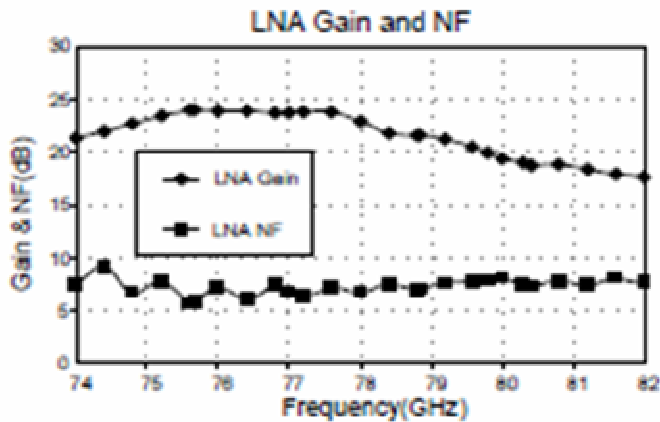
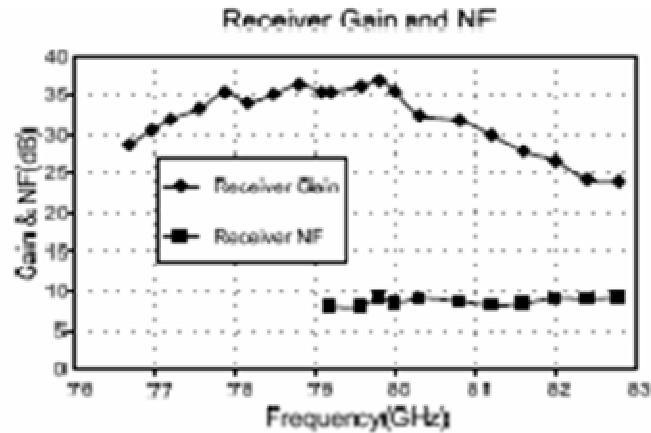


Figure 10.1.7: Chip micrograph.

- CMOSを用い、殆どのワイアレスシステムをワンチップに集積するRF-SoCの開発が進行している
 - 大量品においてはRF-SoCがコスト的にも有利との見方
- アナログ技術中心のRF-CMOSからデジタル技術中心のRF-CMOSに技術が転換し、成功を収めつつある
 - アナログ技術中心:PVT、ミスマッチに弱く、性能、量産性ともに課題
 - デジタル技術中心:ばらつきに強く性能、量産性ともにクリアー
外部部品や調整箇所が少なく、コストも安い
- RF回路にデジタル技術を適用するデジタルRF技術の開発が進められている
 - アイデアはおもしろいが、性能は今一步、さらなる技術開発が必要
- ミリ波用途のRF-CMOS開発が台頭し、電磁波的回路のチップ集積が可能となり、新たな技術領域を拓きつつある